



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

MAX2065

概述

MAX2065 高线性度、模拟/数字调节可变增益放大器(VGA)针对50MHz至1000MHz频率范围的应用而设计,带有两级独立的衰减器(参见典型应用电路)。可通过SPI™兼容接口控制作为从机外设的数字衰减器;也允许以1dB步长通过并行总线控制,可调节范围为31dB。该器件增加了“速射”增益选择,可直接设置在4种增益选项的一种,用户可通过SPI接口预先设置四种增益选项。2个控制引脚允许用户快速选择4种定制衰减的任何一个,无需SPI总线编程。利用外部电压或通过SPI接口控制片上8位DAC实现衰减器模拟调节。

因为三级电路的每一级都具有RF输入和RF输出,通过适当配置可以优化NF(第1级为放大器)、OIP3(最后一级为放大器)或在NF和OIP3之间进行折衷。该器件还包含具有22dB增益的放大器(放大器本身),增益最大时NF为6.5dB(包括衰减器的插入损耗),并提供+42dBm的高OIP3。这些特性使得MAX2065能够为众多接收器和发射器提供一个理想的VGA。

另外,MAX2065采用+5V单电源供电,提供功能完备的解决方案;工作在+3.3V时,性能指标略有降低,可以调节偏置电流在电流损耗和线性度方面进行折衷。器件采用紧凑、带裸焊盘的40引脚、薄型QFN封装(6mm x 6mm)。工作在扩展级温度范围($T_C = -40^{\circ}\text{C}$ 至 $+85^{\circ}\text{C}$)。

应用

IF和RF增益分级设计
温度补偿电路
蜂窝频段WCDMA和cdma2000®基站
GSM 850/GSM 900 EDGE基站
WiMAX和LTE基站以及用户驻地设备
固定宽带无线接入
无线本地环路
军用系统
视频点播(VOD)和DOCSIS®兼容于EDGE QAM调制
电缆调制解调器端接系统(CMTS)

特性

- ◆ 50MHz到1000MHz RF频率范围
- ◆ 引脚兼容的系列产品包括:
MAX2066 (数字VGA)
MAX2067 (模拟VGA)
- ◆ +19.4dB (典型值)最大增益
- ◆ 100MHz带宽内保持0.5dB增益平坦度
- ◆ 62dB增益范围(31dB模拟控制增益 + 31dB数字控制增益)
- ◆ 内置用于模拟衰减控制的DAC
- ◆ 支持4种“速射”预编程衰减选项
快速设置4种定制衰减之一,无需SPI总线编程
理想用于快速响应和信号阻塞保护
避免ADC过驱动
- ◆ 优异的线性指标(配置放大器为最后一级)
+42dBm OIP3
+63dBm OIP2
+19dBm输出1dB压缩点
-67dBc HD2
-83dBc HD3
- ◆ 6.5dB典型噪声系数(NF)
- ◆ 25ns快速数字切换
- ◆ 超低数字VGA过冲/欠冲幅度
- ◆ 单电源+5V供电(可选择+3.3V单电源供电)
- ◆ 优异的外部电流设置电阻,提供降功率/降性能两种工作模式

订购信息

PART	TEMP RANGE	PIN-PACKAGE	PKG CODE
MAX2065ETL+	-40°C to +85°C	40 Thin QFN-EP*	T4066-3
MAX2065ETL+T	-40°C to +85°C	40 Thin QFN-EP*	T4066-3

+表示无铅封装。

*EP = 裸焊盘。

T = 卷带包装。

引脚配置在数据资料的最后给出。

cdma2000是电信工业协会的注册商标。

DOCSIS和CableLabs是Cable Television Laboratories, Inc. (CableLabs®)的注册商标。

SPI是Motorola, Inc.的商标。



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ABSOLUTE MAXIMUM RATINGS

VCC_ to GND-0.3V to +5.5V
 VDD_LOGIC, DATA, $\overline{CS}$, CLK, SER/PAR, VDAC_EN,
 VREF_SELECT.....-0.3V to (VCC_ + 0.3V)
 STATE_A, STATE_B, D0–D4-0.3V to (VCC_ + 0.3V)
 AMP_IN, AMP_OUT, VREF_IN,
 ANALOG_VCTRL-0.3V to (VCC_ + 0.3V)
 ATTEN1_IN, ATTEN1_OUT, ATTEN2_IN,
 ATTEN2_OUT.....-1.2V to + 1.2V
 RSET to GND-0.3V to + 1.2V

RF Input Power (ATTEN1_IN, ATTEN1_OUT,
 ATTEN2_IN, ATTEN2_OUT).....+20dBm
 RF Input Power (AMP_IN).....+18dBm
 Continuous Power Dissipation (Note 1)6.5W
 θ_{JA} (Notes 2, 3).....+38°C/W
 θ_{JC} (Note 3)+10°C/W
 Operating Temperature Range (Note 4).....T_C = -40°C to +85°C
 Maximum Junction Temperature+150°C
 Storage Temperature.....-65°C to +150°C
 Lead Temperature (soldering, 10s).....+300°C

Note 1: Based on junction temperature $T_J = T_C + (\theta_{JC} \times V_{CC} \times I_{CC})$. This formula can be used when the temperature of the exposed pad is known while the device is soldered down to a printed-circuit board (PCB). See the *Applications Information* section for details. The junction temperature must not exceed +150°C.

Note 2: Junction temperature $T_J = T_A + (\theta_{JA} \times V_{CC} \times I_{CC})$. This formula can be used when the ambient temperature of the PCB is known. The junction temperature must not exceed +150°C.

Note 3: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a 4-layer board. For detailed information on package thermal considerations, refer to www.maxim-ic.com.cn/thermal-tutorial.

Note 4: T_C is the temperature on the exposed pad of the package. T_A is the ambient temperature of the device and PCB.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

+3.3V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, high-current (HC) mode, V_{CC} = +3.0V to +3.6V, T_C = -40°C to +85°C. Typical values are at V_{CC} = +3.3V and T_C = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V _{CC}		3.0	3.3	3.6	V
Supply Current	I _{CC}			60	80	mA
LOGIC INPUTS (DATA, $\overline{CS}$, CLK, VDAC_EN, VREF_SELECT, SER/PAR, STATE_A, STATE_B, D0–D4)						
Input High Voltage	V _{IH}			2		V
Input Low Voltage	V _{IL}			0.8		V

+5V SUPPLY DC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, V_{CC} = +4.75V to +5.25V, T_C = -40°C to +85°C. Typical values are at V_{CC} = +5V and T_C = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V _{CC}		4.75	5	5.25	V
Supply Current	I _{CC}	Low-current (LC) mode		73	93	mA
		High-current (HC) mode		124	146	
LOGIC INPUTS (DATA, $\overline{\text{CS}}$, CLK, VD _{AC_EN} , VREF_SELECT, SER/PAR, STATE_A, STATE_B, D0-D4)						
Input High Voltage	V _{IH}		3			V
Input Low Voltage	V _{IL}				0.8	V
Input Current Logic-High	I _{IH}		-1		+1	μA
Input Current Logic-Low	I _{IL}		-1		+1	μA

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+3.3V SUPPLY AC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, $V_{CC} = +3.0V$ to $+3.6V$, $T_C = -40^{\circ}C$ to $+85^{\circ}C$. Typical values are at $V_{CC} = +3.3V$, HC mode with attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^{\circ}C$, unless otherwise noted.) (Note 5)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
RF Frequency Range	f_{RF}	(Notes 6, 7)	50		1000	MHz
Small Signal Gain	G			18.8		dB
Output Third-Order Intercept Point	OIP3	$P_{OUT} = 0dBm/tone$, maximum gain setting		37.5		dBm
Noise Figure	NF	Maximum gain setting		6.7		dB
Total Attenuation Range		Analog and digital combined		61.5		dB

+5V SUPPLY AC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, $V_{CC} = +4.75V$ to $+5.25V$, HC mode with each attenuator set for maximum gain, $50MHz \leq f_{RF} \leq 1000MHz$, $T_C = -40^{\circ}C$ to $+85^{\circ}C$. Typical values are at $V_{CC} = +5.0V$, HC mode, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^{\circ}C$, unless otherwise noted.) (Note 5)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
RF Frequency Range	f_{RF}	(Notes 6, 7)	50		1000	MHz
Small Signal Gain	G	200MHz		19.4		dB
		350MHz, $T_C = +25^{\circ}C$	17.5	18.7	19.7	
		450MHz		18.2		
		750MHz		16.4		
		900MHz		15.6		
Gain Variation vs. Temperature				-0.006		dB/ $^{\circ}C$
Gain Flatness vs. Frequency		Any 100MHz frequency band from 50MHz to 500MHz		0.5		dB
Noise Figure	NF	200MHz		6.5		dB
		350MHz, $T_C = +25^{\circ}C$ (Note 7)		6.8	8	
		450MHz		7		
		750MHz		7.8		
		900MHz		8.2		
Total Attenuation Range		Analog and digital combined		61.5		dB
Output Second-Order Intercept Point	OIP2	$P_{OUT} = 0dBm/tone$, $\Delta f = 1MHz$, $f_1 + f_2$		63		dBm
Output Third-Order Intercept Point	OIP3	$P_{OUT} = 0dBm/tone$, HC mode, $\Delta f = 1MHz$	200MHz	42		dBm
			350MHz	40		
			450MHz	39		
			750MHz	36		
			900MHz	35		
		$P_{OUT} = 0dBm/tone$, LC mode, $\Delta f = 1MHz$	200MHz	40		
			350MHz	38		
			450MHz	37		
			750MHz	35		
			900MHz	33		

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+5V SUPPLY AC ELECTRICAL CHARACTERISTICS (continued)

(Typical Application Circuit, $V_{CC} = +4.75$ to $+5.25$ V, HC mode with each attenuator set for maximum gain, $50\text{MHz} \leq f_{RF} \leq 1000\text{MHz}$, $T_C = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are at $V_{CC} = +5.0$ V, HC mode, $P_{IN} = -20\text{dBm}$, $f_{RF} = 200\text{MHz}$, and $T_C = +25^\circ\text{C}$, unless otherwise noted.) (Note 5)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Output -1dB Compression Point	P _{1dB}	350MHz, T _C = +25°C (Note 8)		17	18.7		dBm
Second Harmonic		P _{OUT} = +3dBm, f _{RF} = 200MHz, T _C = +25°C (Note 7)		-60	-67		dBc
Third Harmonic		P _{OUT} = +3dBm, f _{RF} = 200MHz, T _C = +25°C (Note 7)		-71	-83		dBc
Input Return Loss		50Ω source, maximum gain setting			18		dB
Output Return Loss		50Ω load, maximum gain setting			18		dB
DIGITAL ATTENUATOR							
Insertion Loss					2.5		dB
Input Second-Order Intercept Point	IIP2	P _{RF1} = 0dBm, P _{RF2} = 0dBm, Δf = 1MHz, f ₁ + f ₂			52		dBm
Input Third-Order Intercept Point	IIP3	P _{RF1} = 0dBm, P _{RF2} = 0dBm, Δf = 1MHz			41		dBm
Attenuation Range					31.2		dB
Step Size					1		dB
Relative Step Accuracy					0.2		dB
Absolute Step Accuracy					0.45		dB
Insertion Phase Step		f _{RF} = 170MHz	0dB to 16dB		4.8		Degrees
			24dB		8		
			31dB		10.8		
Amplitude Overshoot/Undershoot		Between any two states	ET = 15ns		1.0		dB
			ET = 40ns		0.05		
Switching Speed		RF settled to within ±0.1dB	31dB to 0dB		25		ns
			0dB to 31dB		21		
Input Return Loss		50Ω source			19		dB
Output Return Loss		50Ω load			19		dB
ANALOG ATTENUATOR							
Insertion Loss					1.2		dB
Input Second-Order Intercept Point	IIP2	P _{RF1} = 0dBm, P _{RF2} = 0dBm, maximum gain setting, Δf = 1MHz, f ₁ + f ₂			70		dBm
Input Third-Order Intercept Point	IIP3	P _{RF1} = 0dBm, P _{RF2} = 0dBm, maximum gain setting, Δf = 1MHz			36		dBm
Attenuation Range		Analog control input			31.1		dB
Gain Control Slope		Analog control input			-12.5		dB/V
Maximum Gain Control Slope		Over analog control input range			-35		dB/V
Insertion Phase Change		Over analog control input range			18		Degrees
Group Delay		Maximum gain setting			0.98		ns
Group Delay vs. Control Voltage		Over analog control input range			-0.25		ns
Analog Control Input Range				0.25		2.75	V

50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

+5V SUPPLY AC ELECTRICAL CHARACTERISTICS (continued)

(Typical Application Circuit, $V_{CC} = +4.75$ to $+5.25V$, HC mode with each attenuator set for maximum gain, $50MHz \leq f_{RF} \leq 1000MHz$, $T_C = -40^\circ C$ to $+85^\circ C$. Typical values are at $V_{CC} = +5.0V$, HC mode, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, unless otherwise noted.) (Note 5)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Analog Control Input Impedance				80		kΩ
Input Return Loss		50Ω source		22		dB
Output Return Loss		50Ω load		22		dB
D/A CONVERTER						
Number of Bits				8		Bits
Output Voltage		DAC code = 00000000			0.25	V
		DAC code = 11111111	2.75			
SERIAL PERIPHERAL INTERFACE (SPI)						
Maximum Clock Speed	fCLK			20		MHz
Data-to-Clock Setup Time	tCS			2		ns
Data-to-Clock Hold Time	tCH			2.5		ns
Clock-to- $\overline{\text{CS}}$ Setup Time	tES			3		ns
$\overline{\text{CS}}$ Positive Pulse Width	tEW			7		ns
$\overline{\text{CS}}$ Setup Time	tEWS			3.5		ns
Clock Pulse Width	tCW			5		ns

Note 5: All limits include external component losses. Output measurements are performed at RF output port of the *Typical Application Circuit*.

Note 6: Operating outside this range is possible, but with degraded performance of some parameters.

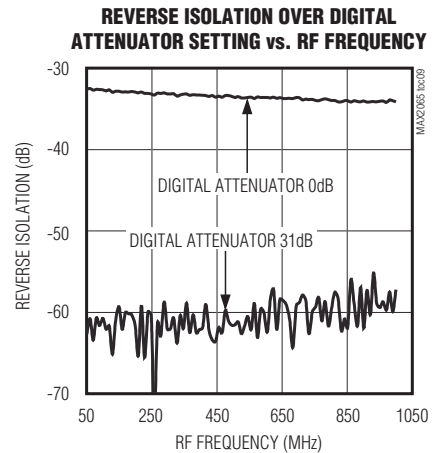
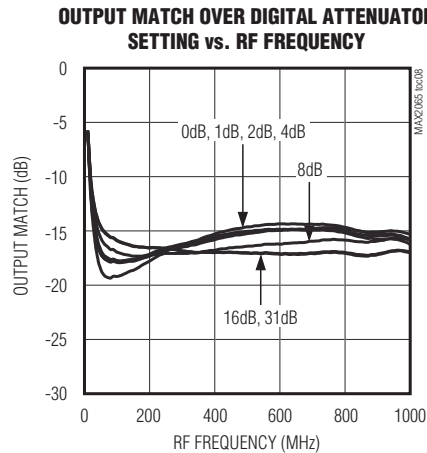
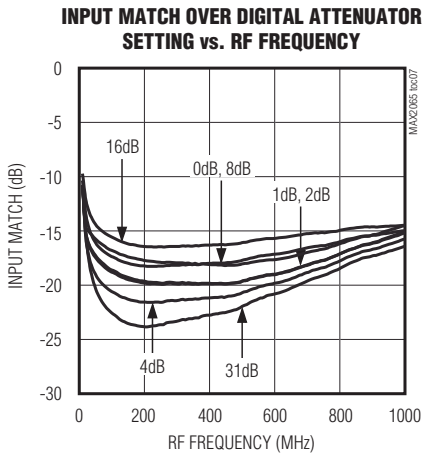
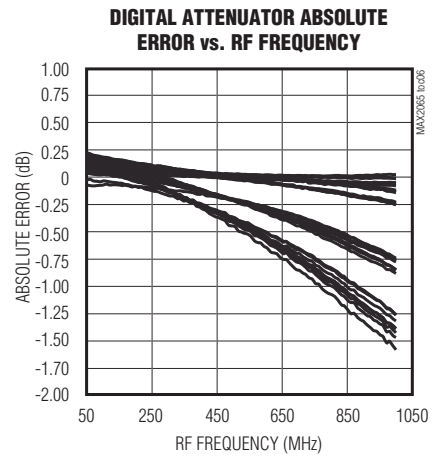
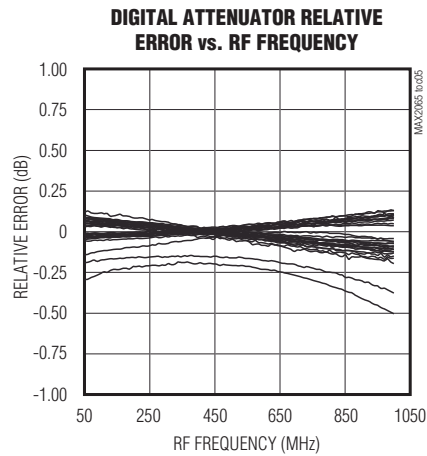
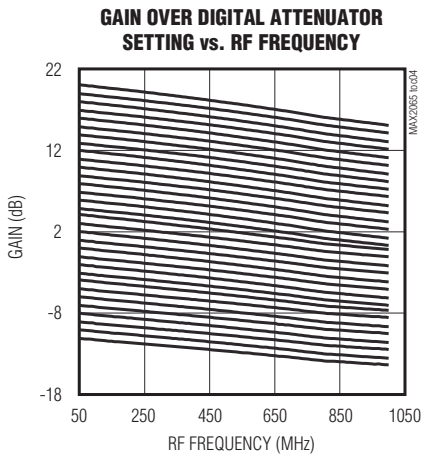
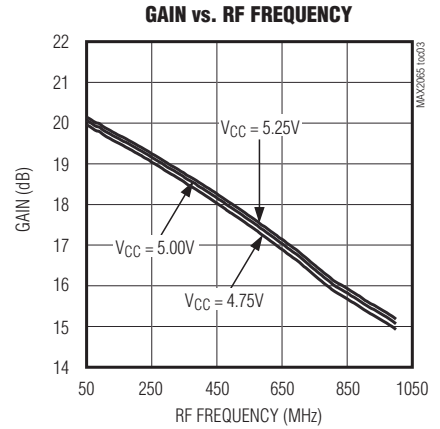
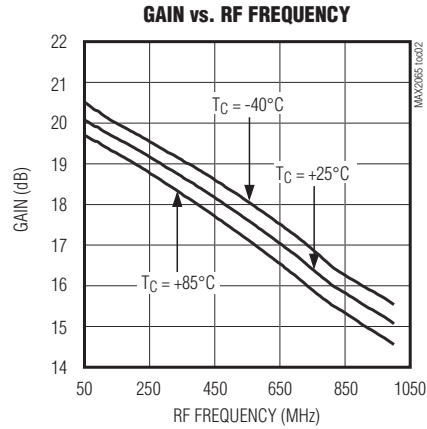
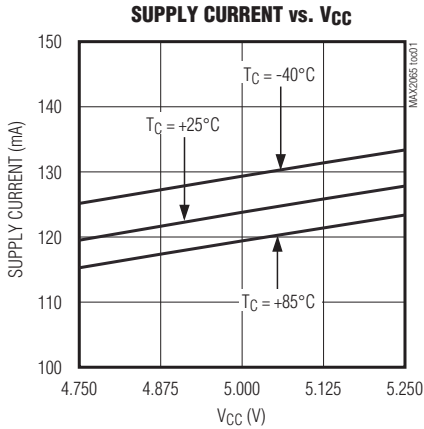
Note 7: Guaranteed by design and characterization.

Note 8: It is advisable not to operate continuously the VGA RF input above +15dBm.

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性

($V_{CC} = +5.0V$, HC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



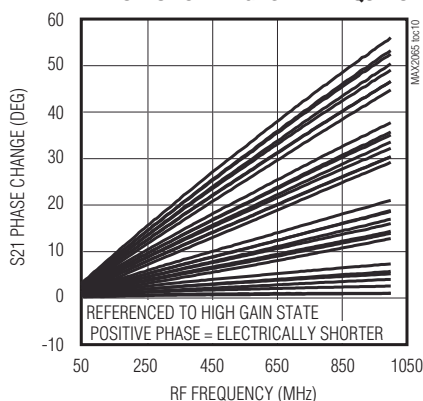
50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

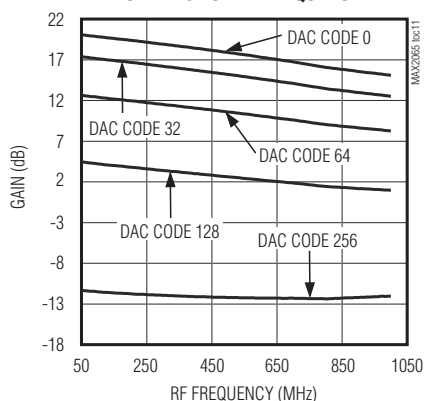
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MAX2065

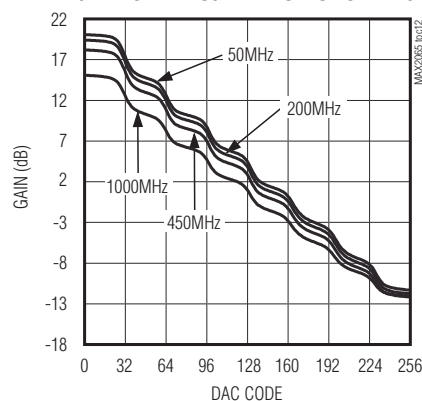
S21 PHASE CHANGE OVER DIGITAL ATTENUATOR SETTING vs. RF FREQUENCY



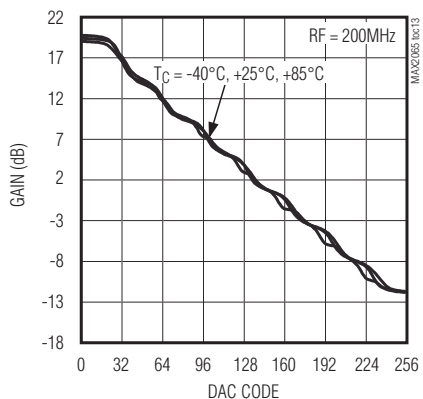
GAIN OVER ANALOG ATTENUATOR SETTING vs. RF FREQUENCY



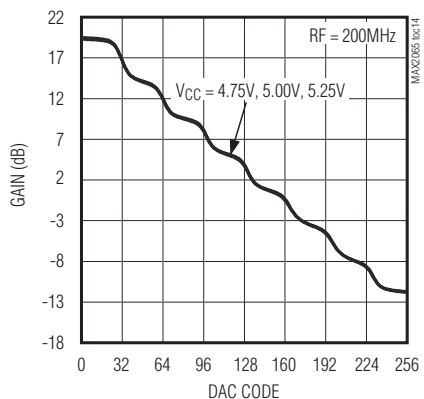
GAIN vs. ANALOG ATTENUATOR SETTING



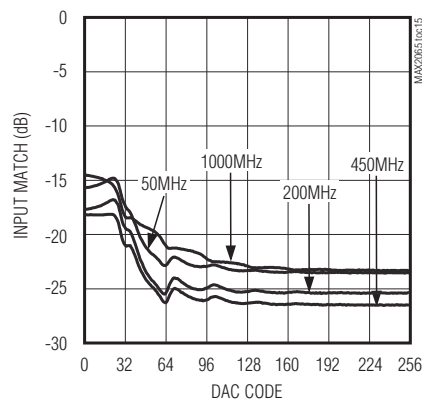
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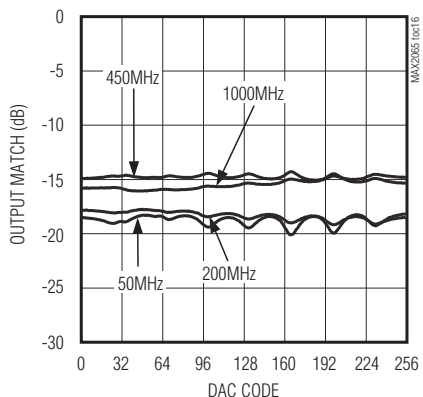
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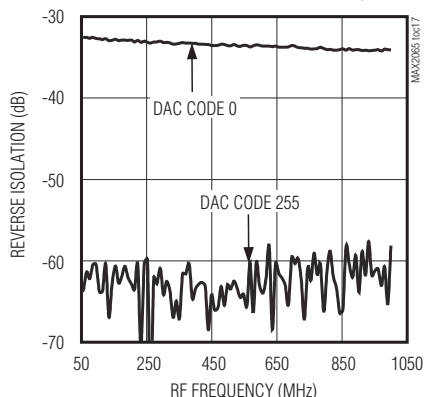
INPUT MATCH vs. ANALOG ATTENUATOR SETTING



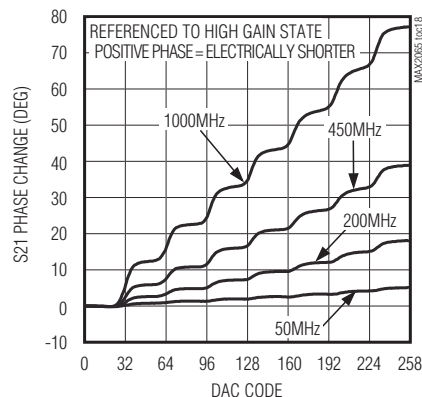
OUTPUT MATCH vs. ANALOG ATTENUATOR SETTING



REVERSE ISOLATION OVER ANALOG ATTENUATOR SETTING vs. RF FREQUENCY



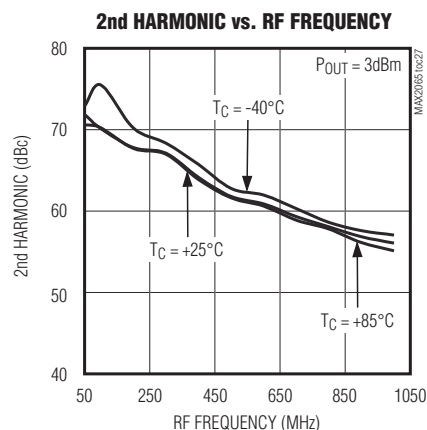
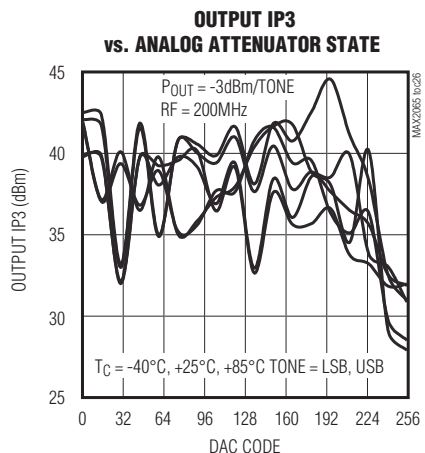
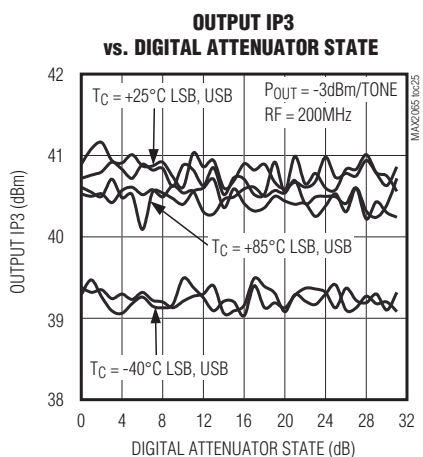
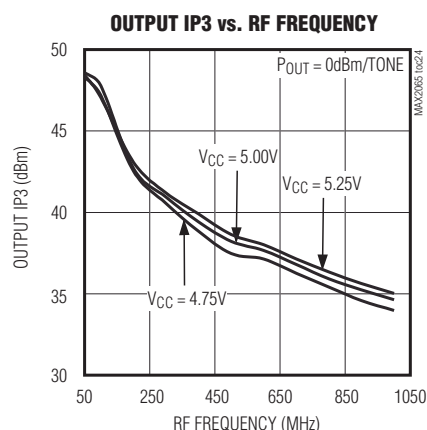
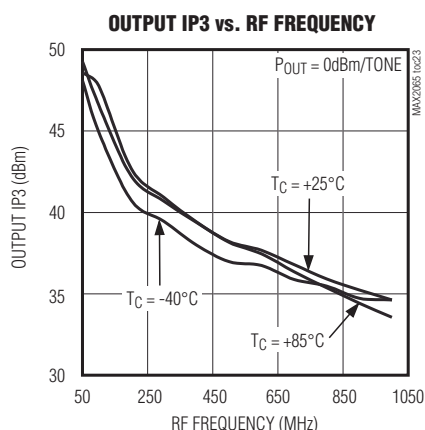
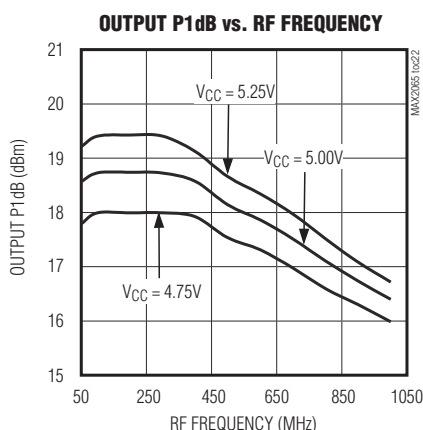
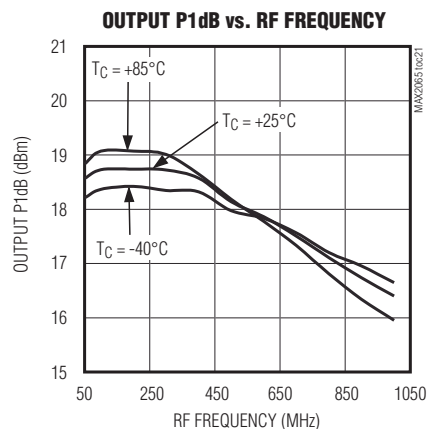
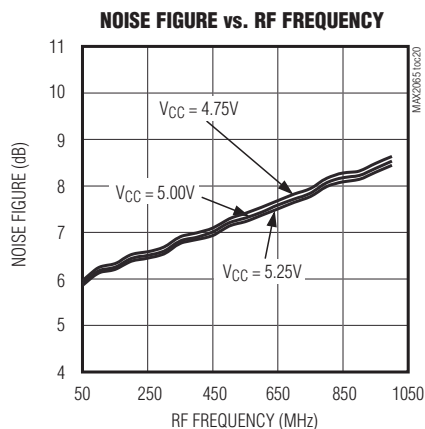
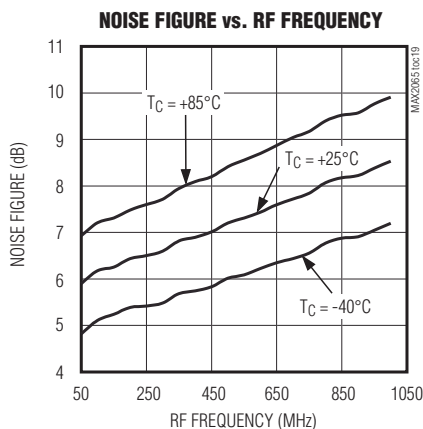
S21 PHASE CHANGE vs. ANALOG ATTENUATOR SETTING



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

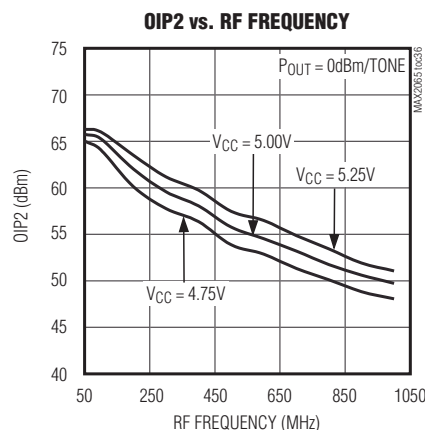
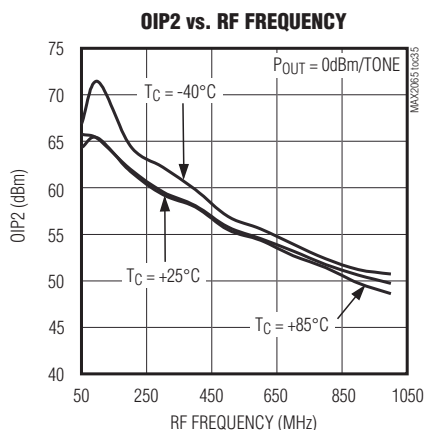
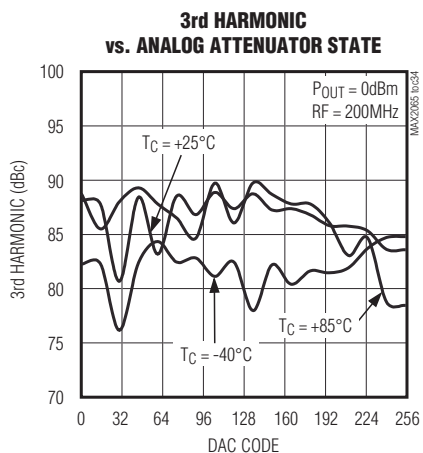
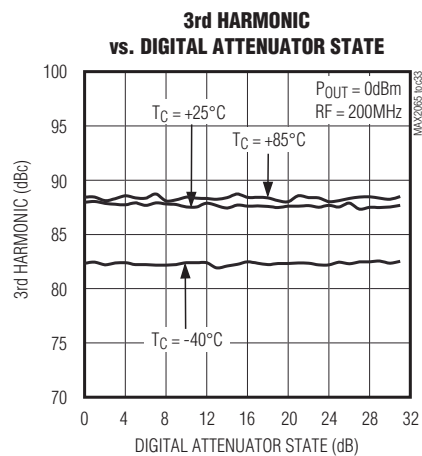
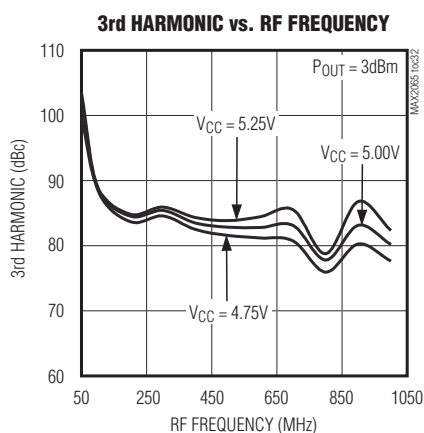
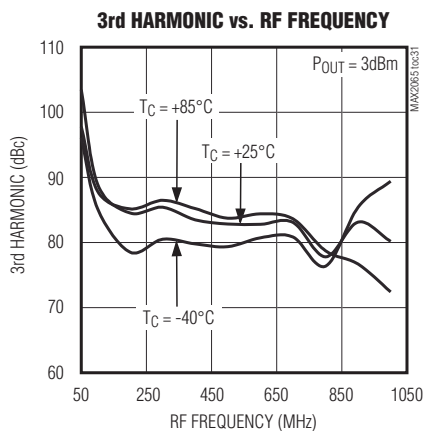
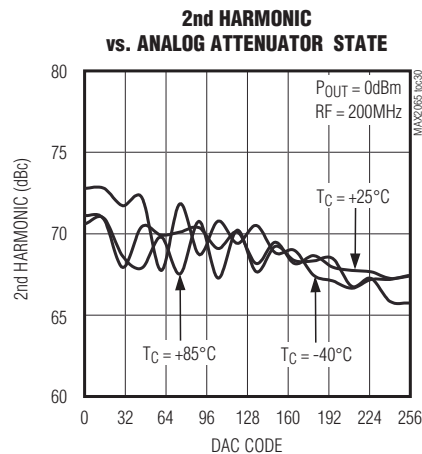
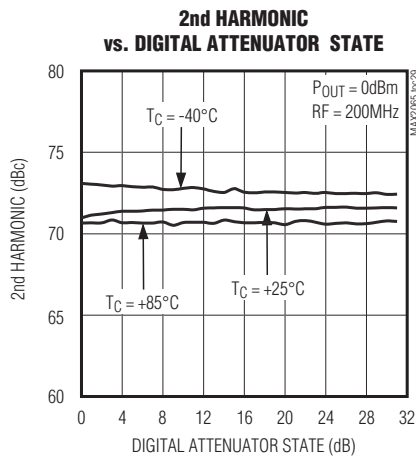
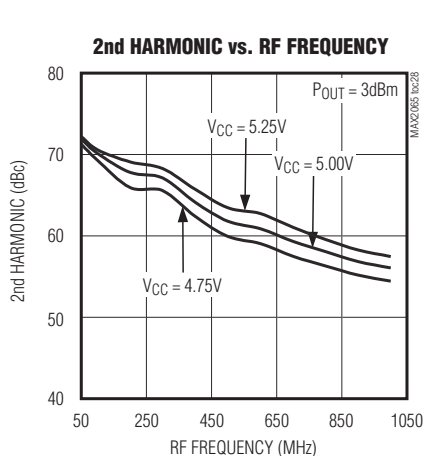
($V_{CC} = +5.0V$, **HC mode**, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

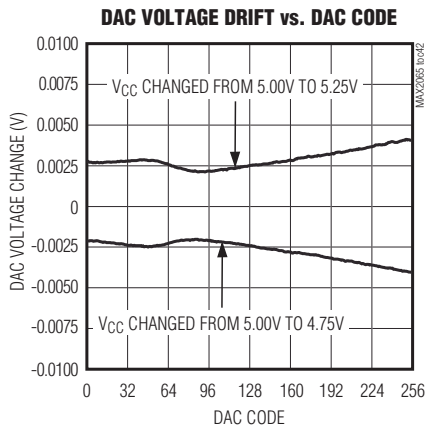
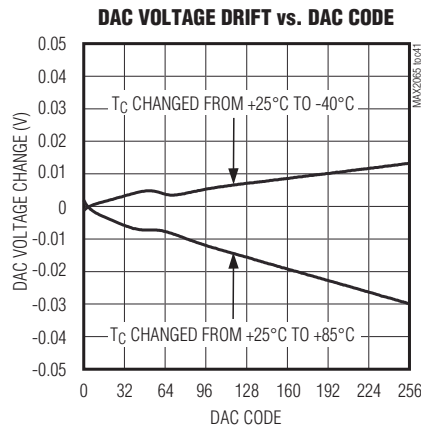
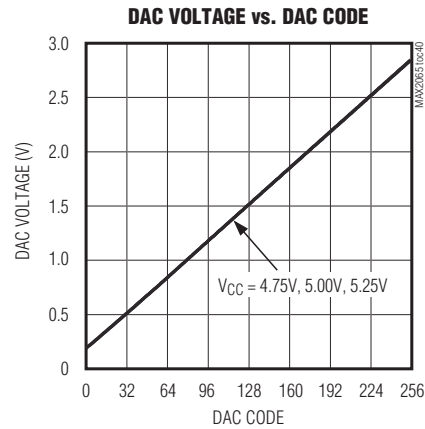
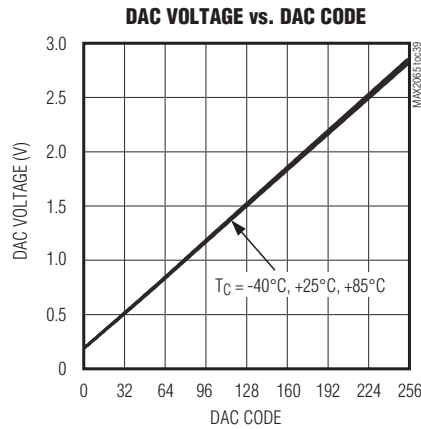
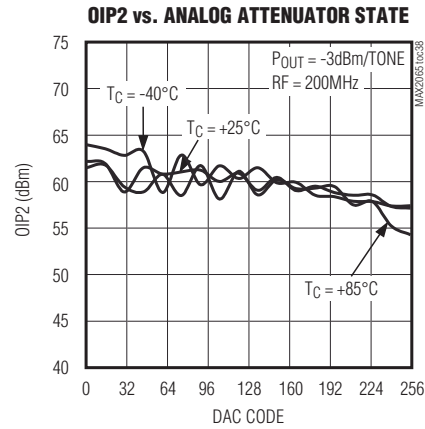
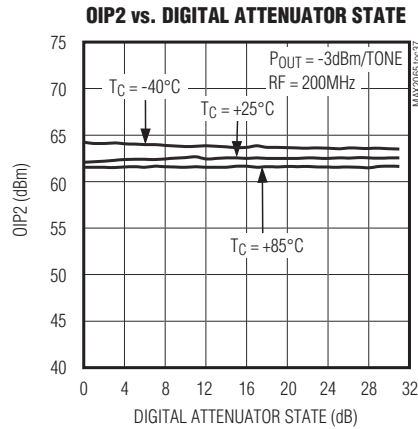
($V_{CC} = +5.0V$, HC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

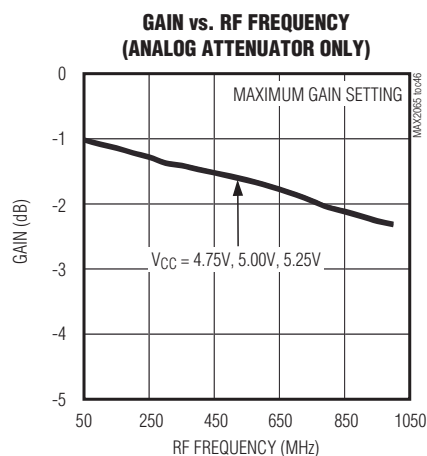
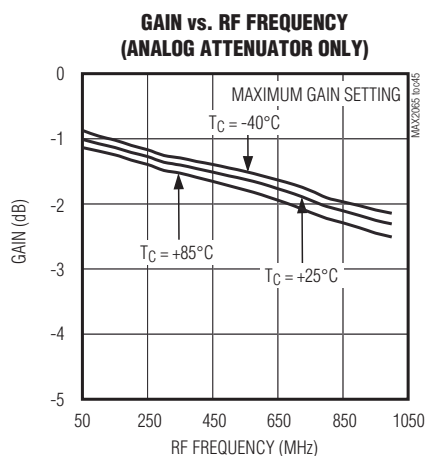
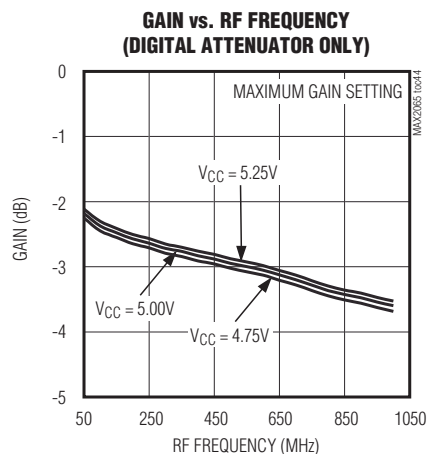
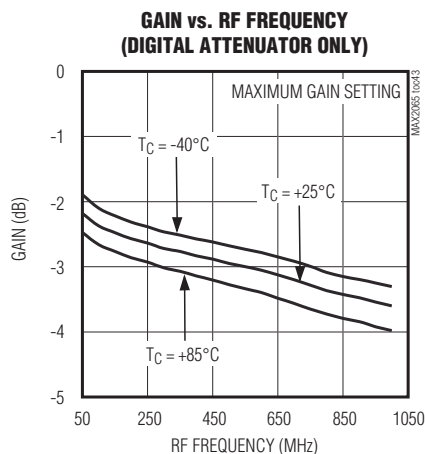
($V_{CC} = +5.0V$, **HC mode**, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

典型工作特性(续)

($V_{CC} = +5.0V$, attenuator only, maximum gain, $P_{IN} = -20dBm$ and $T_C = +25^{\circ}C$, unless otherwise noted.)

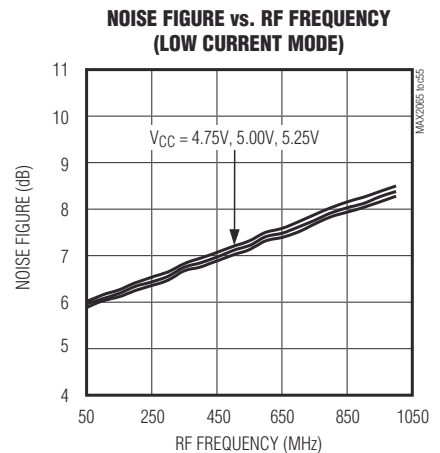
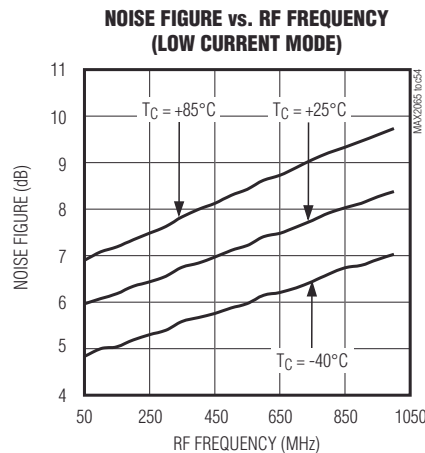
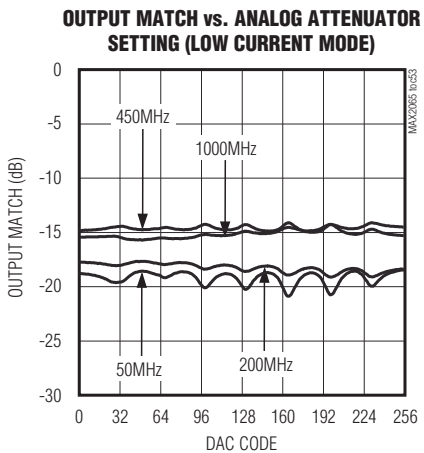
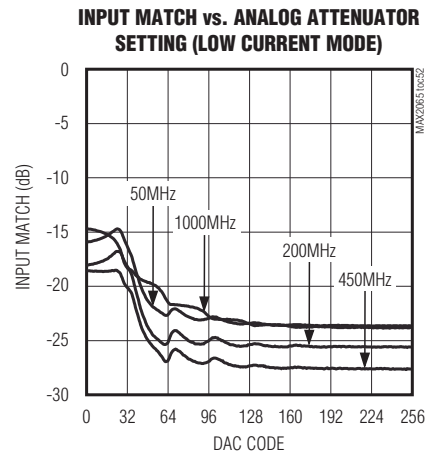
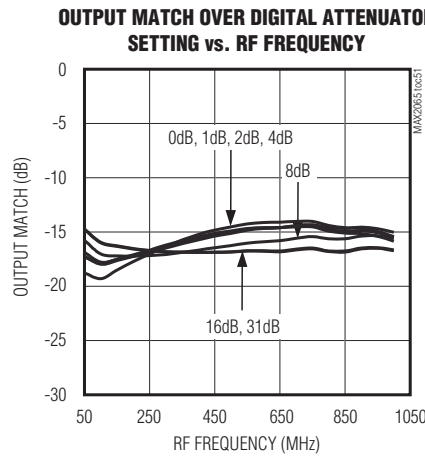
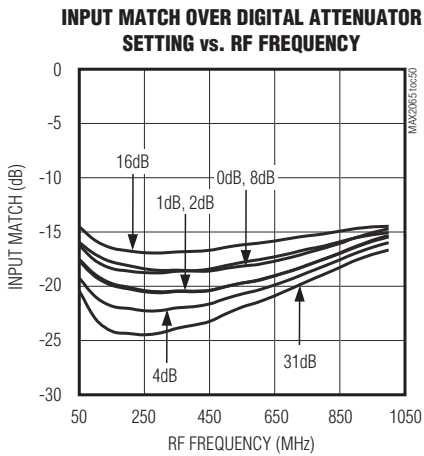
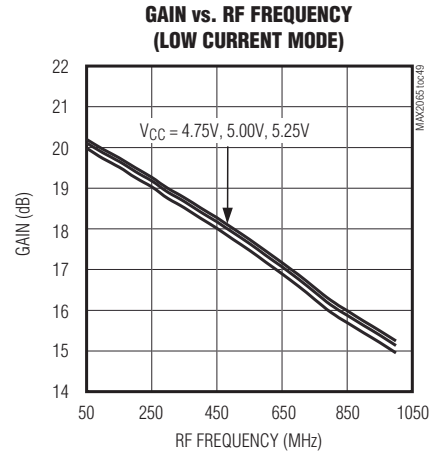
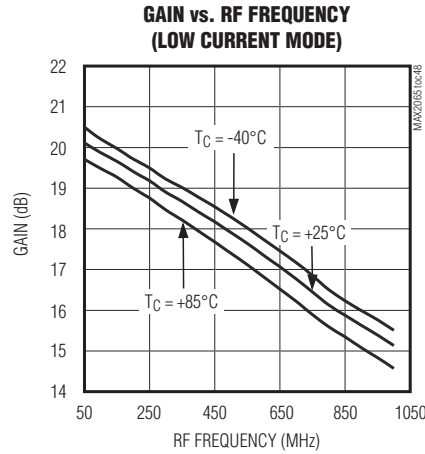
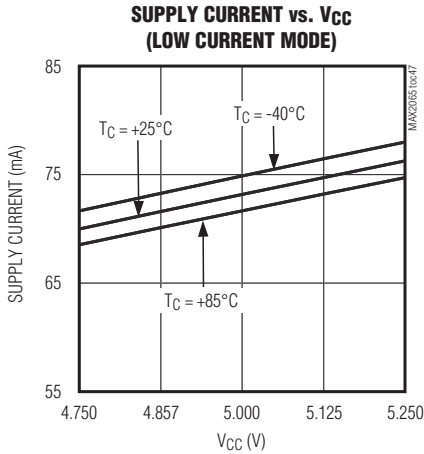


MAX2065

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

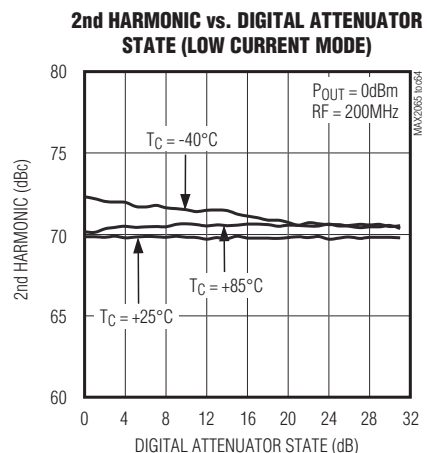
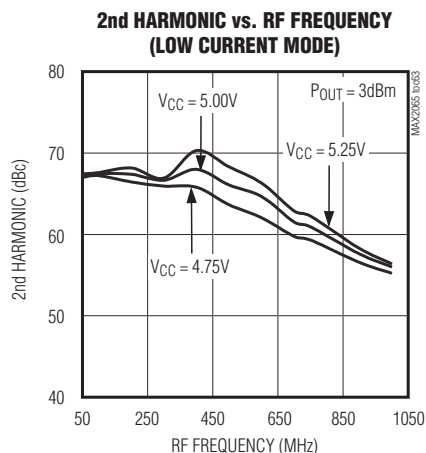
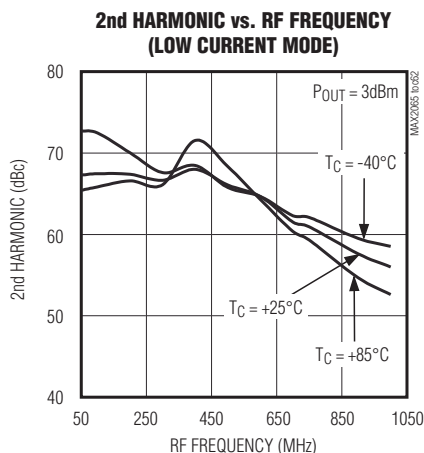
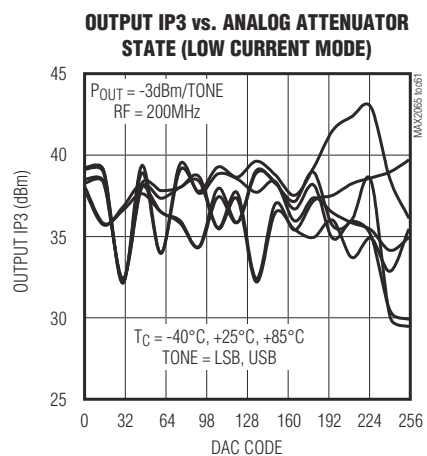
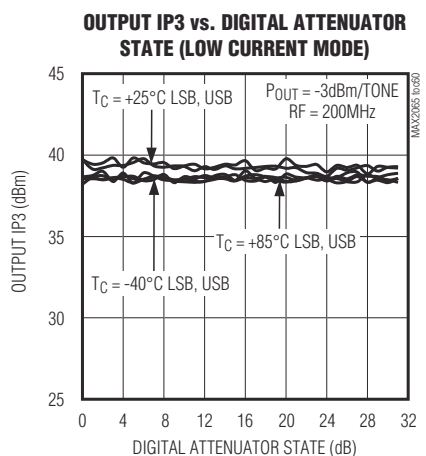
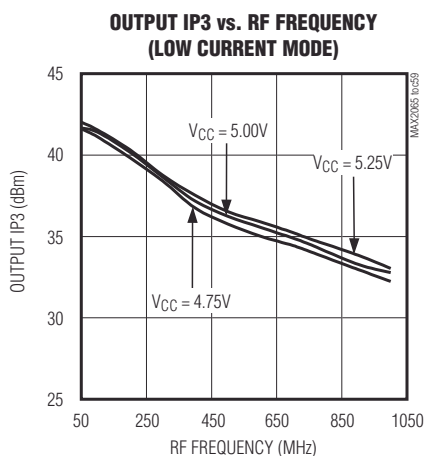
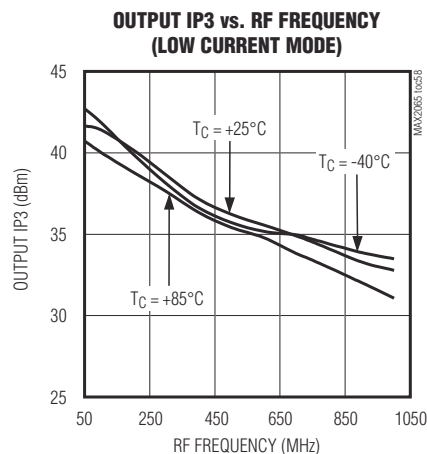
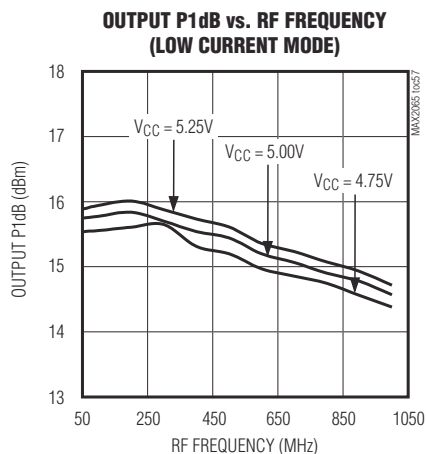
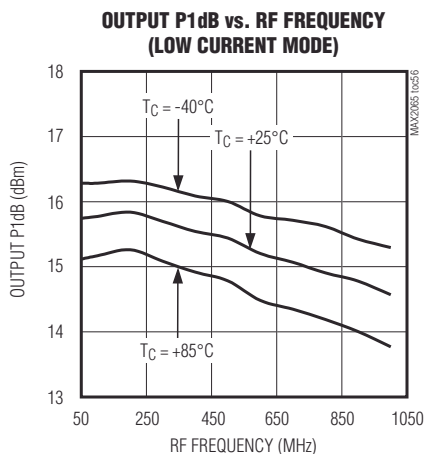
($V_{CC} = +5.0V$, LC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

($V_{CC} = +5.0V$, LC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal reference used, unless otherwise noted.)

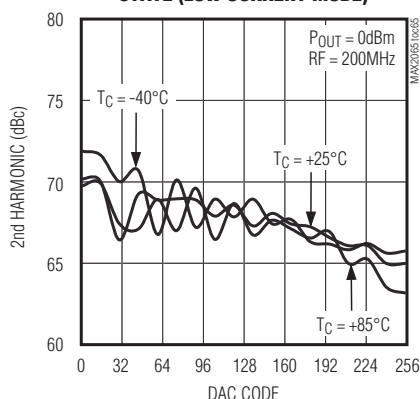


50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

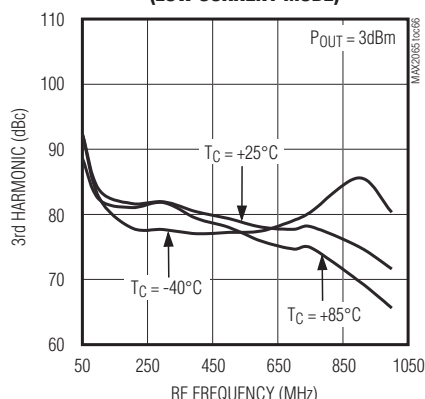
典型工作特性(续)

($V_{CC} = +5.0V$, LC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal reference used, unless otherwise noted.)

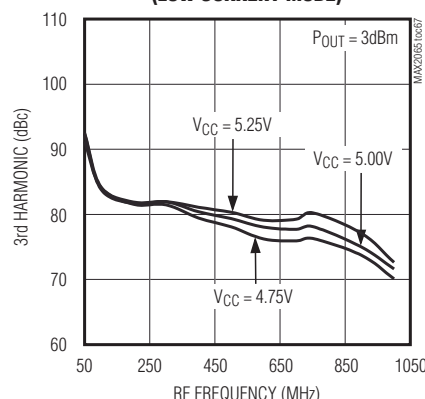
2nd HARMONIC vs. ANALOG ATTENUATOR STATE (LOW CURRENT MODE)



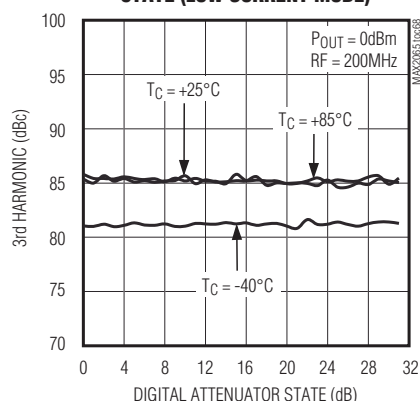
3rd HARMONIC vs. RF FREQUENCY (LOW CURRENT MODE)



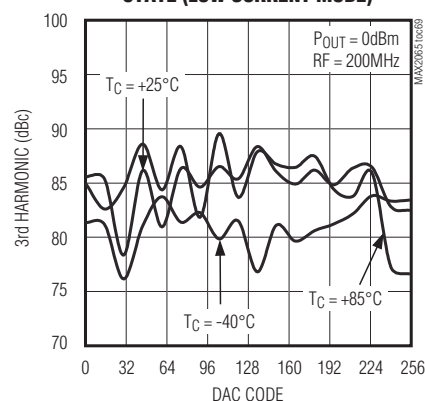
3rd HARMONIC vs. RF FREQUENCY (LOW CURRENT MODE)



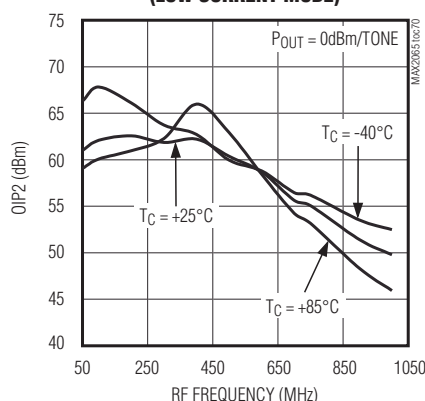
3rd HARMONIC vs. DIGITAL ATTENUATOR STATE (LOW CURRENT MODE)



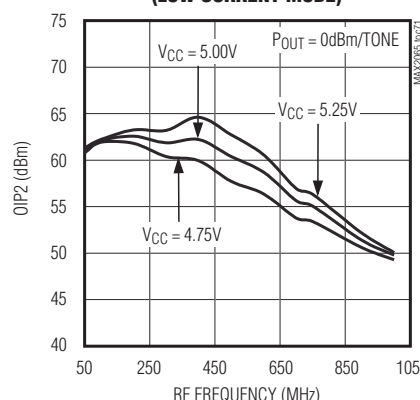
3rd HARMONIC vs. ANALOG ATTENUATOR STATE (LOW CURRENT MODE)



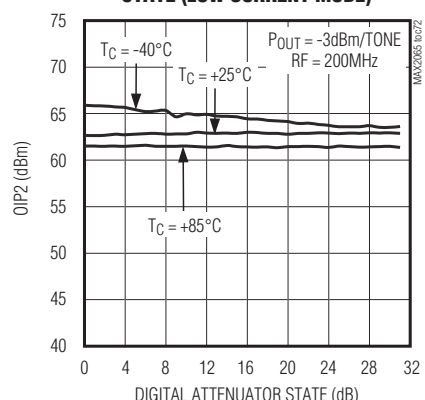
OIP2 vs. RF FREQUENCY (LOW CURRENT MODE)



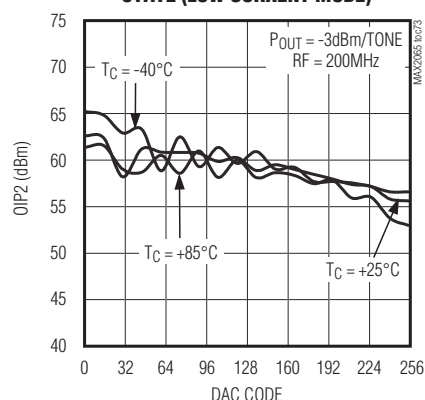
OIP2 vs. RF FREQUENCY (LOW CURRENT MODE)



OIP2 vs. DIGITAL ATTENUATOR STATE (LOW CURRENT MODE)



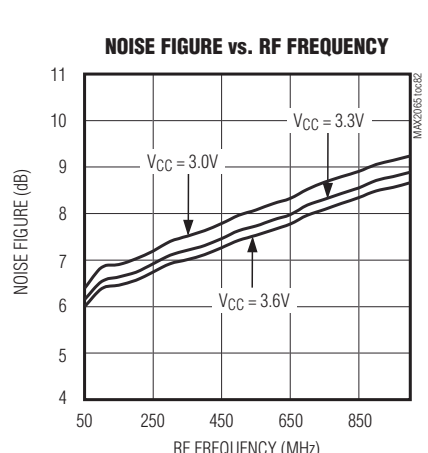
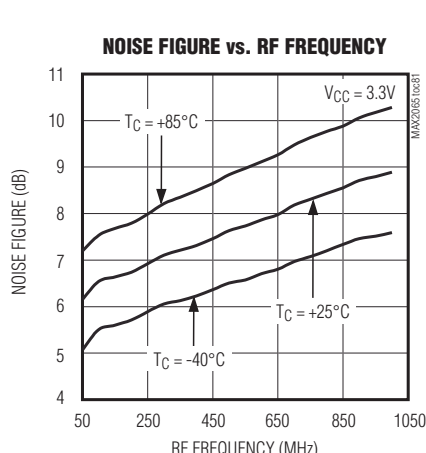
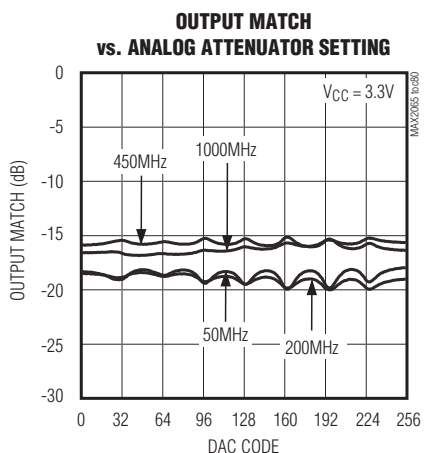
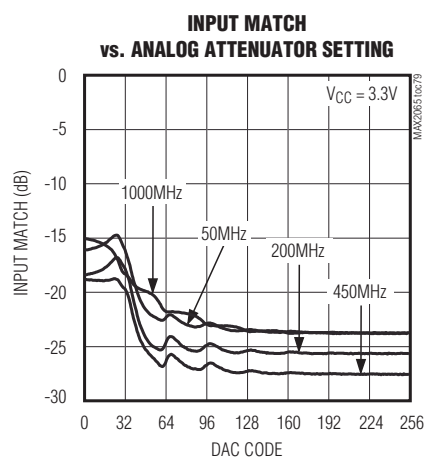
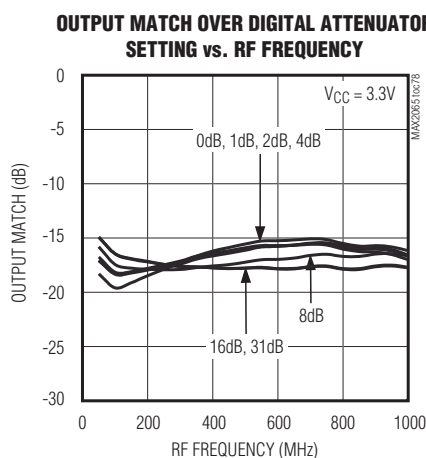
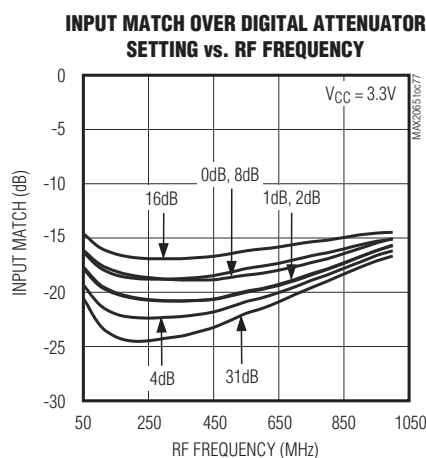
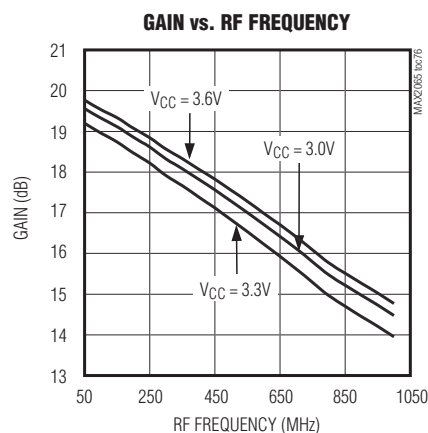
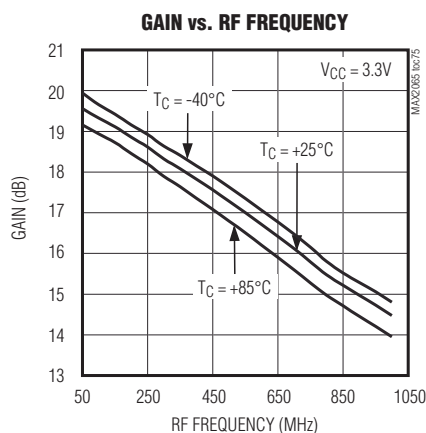
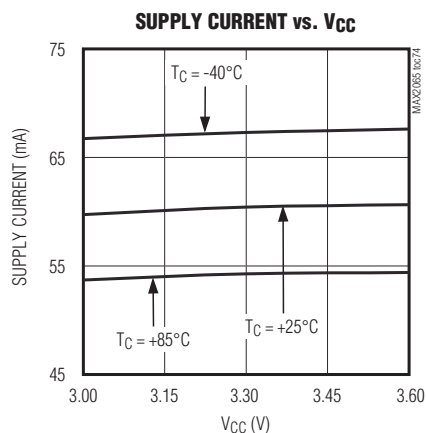
OIP2 vs. ANALOG ATTENUATOR STATE (LOW CURRENT MODE)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

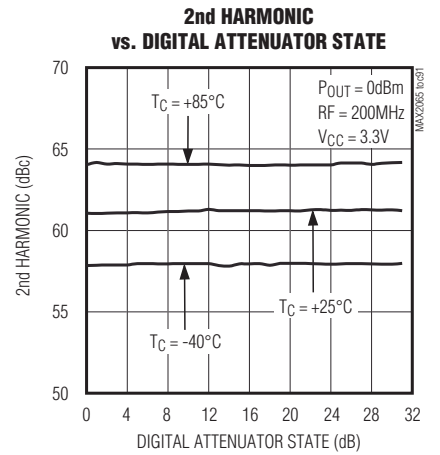
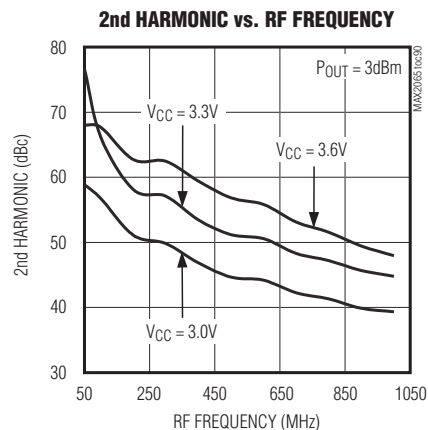
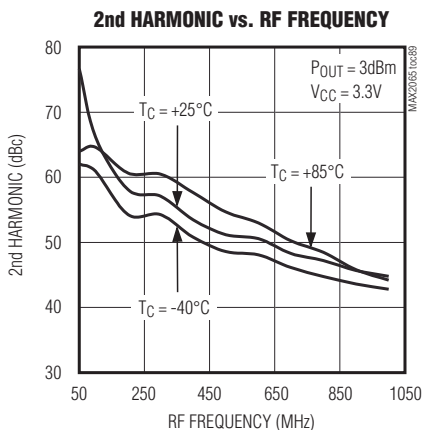
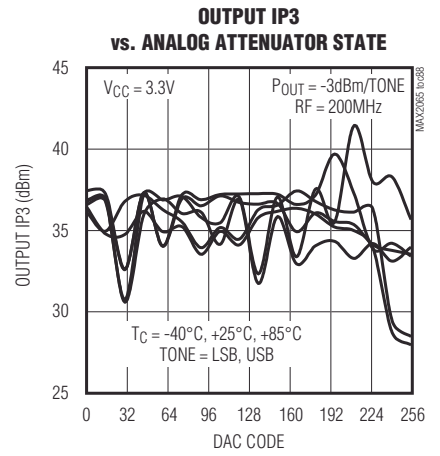
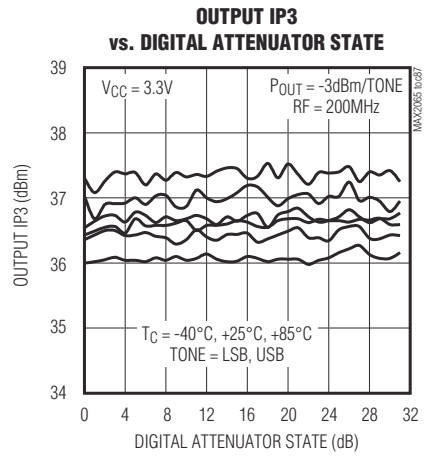
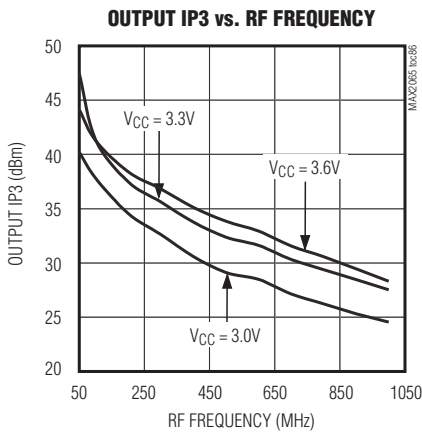
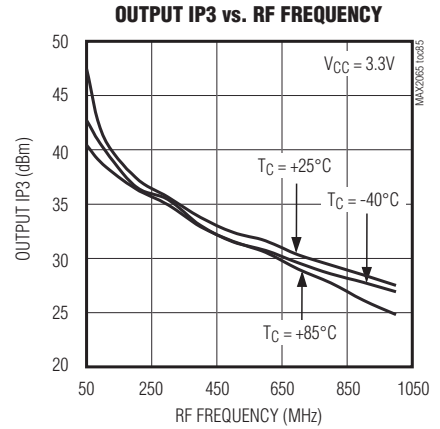
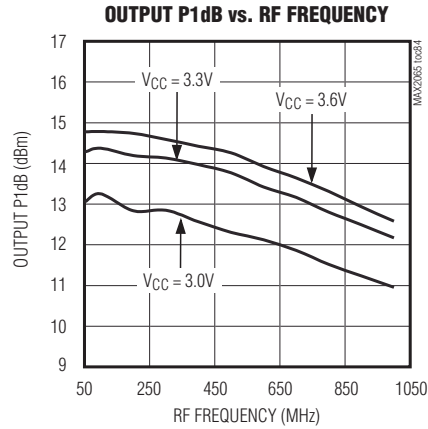
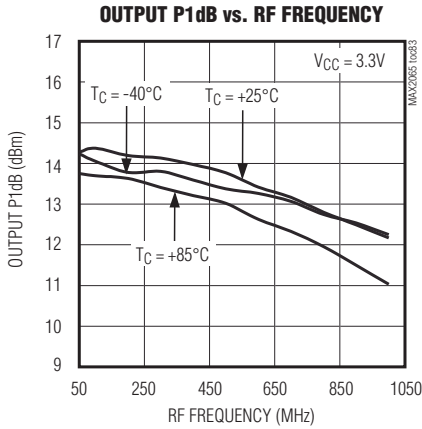
($V_{CC} = +3.3V$, HC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

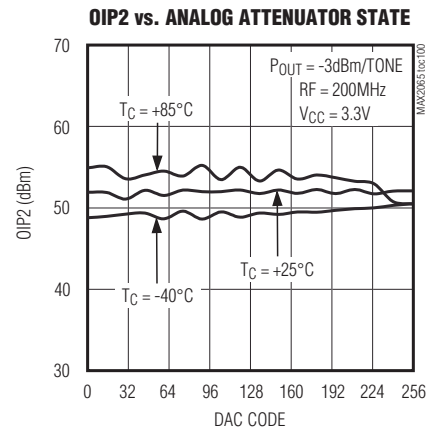
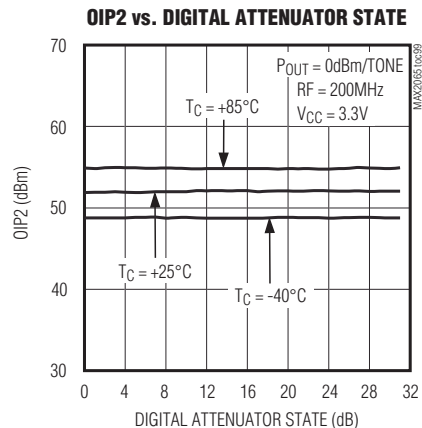
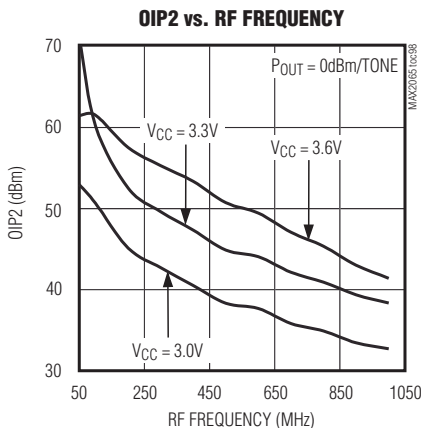
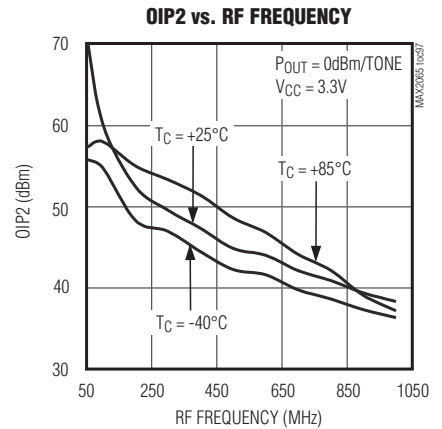
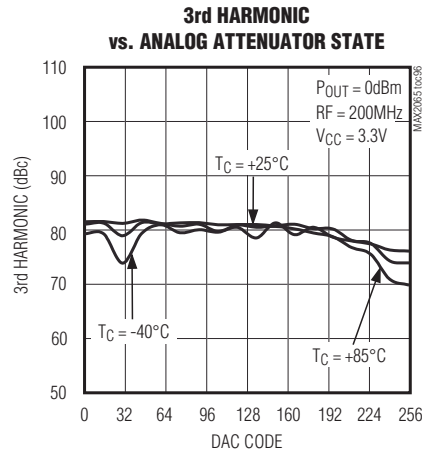
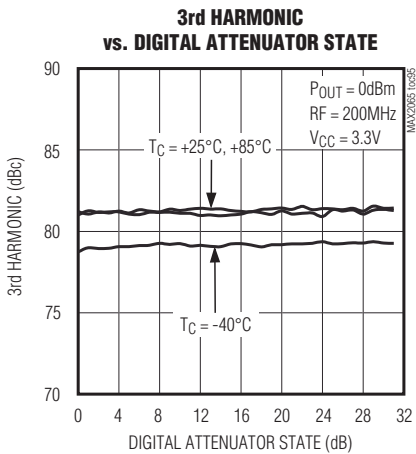
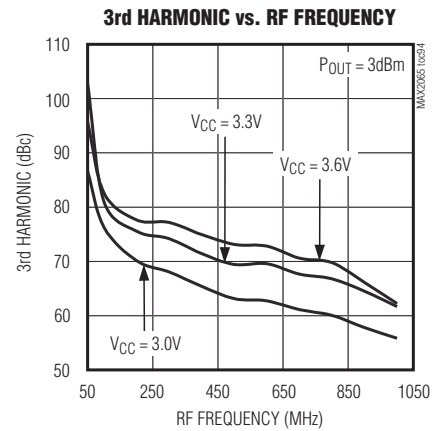
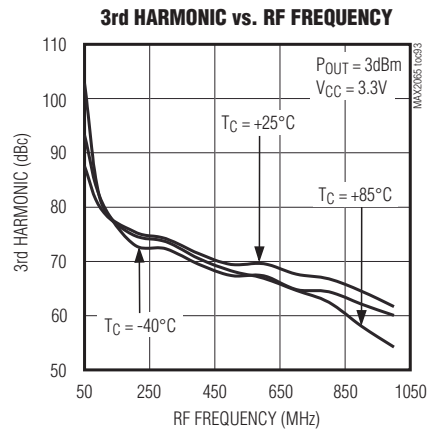
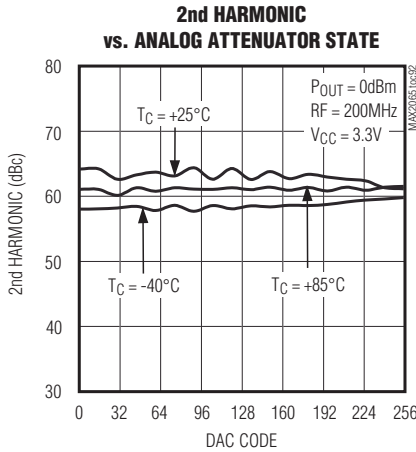
($V_{CC} = +3.3V$, **HC mode**, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

典型工作特性(续)

($V_{CC} = +3.3V$, HC mode, both attenuators set for maximum gain, $P_{IN} = -20dBm$, $f_{RF} = 200MHz$, and $T_C = +25^\circ C$, internal DAC reference used, unless otherwise noted.)



50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

引脚说明

引脚	名称	功能															
1, 16, 19, 22, 24–28, 30, 31, 33–36	GND	地。															
2	VREF_SELECT	DAC基准电压选择逻辑输入。逻辑1 = 内部DAC基准电压；逻辑0 = 外部DAC基准电压。当VDAC_EN = 逻辑0时，逻辑输入被禁用(可忽略)。															
3	VDAC_EN	DAC使能/关闭控制逻辑输入。逻辑0 = 关闭DAC电路；逻辑1 = 打开DAC电路。															
4	DATA	SPI数字数据输入。															
5	CLK	SPI数字时钟输入。															
6	$\overline{CS}$	SPI数字片选输入。															
7	VDD_LOGIC	数字逻辑电路供电输入。															
8	SER/PAR	数字衰减器SPI或并行控制选择输入。逻辑0 = 并行控制；逻辑1 = 串行控制。															
9	STATE_A	数字衰减器预编程衰减状态逻辑输入。															
10	STATE_B	<table> <tr> <th>状态A</th><th>状态B</th><th>数字衰减器</th></tr> <tr> <td>逻辑电平 = 0</td><td>逻辑电平 = 0</td><td>预编程状态1</td></tr> <tr> <td>逻辑电平 = 1</td><td>逻辑电平 = 0</td><td>预编程状态2</td></tr> <tr> <td>逻辑电平 = 0</td><td>逻辑电平 = 1</td><td>预编程状态3</td></tr> <tr> <td>逻辑电平 = 1</td><td>逻辑电平 = 1</td><td>预编程状态4</td></tr> </table>	状态A	状态B	数字衰减器	逻辑电平 = 0	逻辑电平 = 0	预编程状态1	逻辑电平 = 1	逻辑电平 = 0	预编程状态2	逻辑电平 = 0	逻辑电平 = 1	预编程状态3	逻辑电平 = 1	逻辑电平 = 1	预编程状态4
状态A	状态B	数字衰减器															
逻辑电平 = 0	逻辑电平 = 0	预编程状态1															
逻辑电平 = 1	逻辑电平 = 0	预编程状态2															
逻辑电平 = 0	逻辑电平 = 1	预编程状态3															
逻辑电平 = 1	逻辑电平 = 1	预编程状态4															
11	D4	16dB衰减器逻辑输入。逻辑0 = 关闭；逻辑1 = 使能。															
12	D3	8dB衰减器逻辑输入。逻辑0 = 关闭；逻辑1 = 使能。															
13	D2	4dB衰减器逻辑输入。逻辑0 = 关闭；逻辑1 = 使能。															
14	D1	2dB衰减器逻辑输入。逻辑0 = 关闭；逻辑1 = 使能。															
15	D0	1dB衰减器逻辑输入。逻辑0 = 关闭；逻辑1 = 使能。															
17	AMP_OUT	放大器驱动输出(50Ω)。															
18	RSET	放大器驱动偏置电流设置，请参考外部偏置部分。															
20	AMP_IN	放大器驱动输入(50Ω)。															
21	VCC_AMP	放大器驱动电源输入。															
23	ATTEN2_OUT	5位数字衰减器输出(50Ω)。															
29	ATTEN2_IN	5位数字衰减器输入(50Ω)。															
32	ATTEN1_OUT	模拟衰减器输出(50Ω)。															
37	ATTEN1_IN	模拟衰减器输入(50Ω)。															
38	VCC_ANALOG	模拟偏置和控制电路电源输入。															
39	ANALOG_VCTRL	模拟衰减器控制电压输入。															
40	VREF_IN	外部DAC基准电压输入。															
—	EP	裸焊盘，内部连接到GND。将EP连接至GND有利于改善RF性能和散热。															

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

详细说明

MAX2065高线性度、模拟/数字可变增益放大器是一款通用的高性能放大器，针对50MHz至1000MHz频率范围、50Ω系统接口的应用而设计。

MAX2065集成了一个数字衰减器和一个模拟衰减器可提供62dB的增益控制，同时可优化放大器驱动设计来提供高增益、高IP3、低噪声系数和低功耗指标。在对线性度要求不高的应用中，可通过调节外部电阻改变放大器的偏置电流，以进一步降低功耗。

可通过SPI兼容接口控制作为从机外设的数字衰减器；也允许以1dB步长通过并行总线控制，可调节范围为31dB。该器件还增加了“速射”增益选择，直接将增益设置在4种选项(用户可通过SPI接口预先设置)的一种。2个控制引脚允许用户快速选择4种定制衰减的任何一个，无需SPI总线编程。利用外部电压或通过SPI接口控制片上8位DAC，实现衰减器的模拟调节。因为三级电路的每一级都具有RF输入和RF输出，通过适当配置可以优化NF(第1级为放大器)、OIP3(最后一级为放大器)或在NF和OIP3之间进行折衷。该器件还包含具有22dB增益的放大器(放大器本身)，增益最大时NF为6.5dB(包括两个衰减器的插入损耗)，并提供+42dBm的高OIP3。这些特性使得MAX2065能够为众多接收器和发射器提供一个理想的VGA。

另外，MAX2065采用+5V单电源供电，提供功能完备的解决方案；工作在+3.3V时，性能指标略有降低，可调节偏置电流在电流损耗和线性度方面进行折衷。

模拟和5位数字衰减器控制

MAX2065集成了一个模拟衰减器和一个5位数字衰减器，用于实现高动态范围控制。该模拟衰减器具有31dB的动态范围，并可利用外部电压或通过3线串行外设接口(SPI)控制片上8位DAC实现衰减器调节。该数字衰减器具有31dB控制范围，1dB步长，并可通过3线SPI接口设置。请参考应用信息和表1所示衰减器设置，获得更多信息。这些衰减器可用于静态和动态功率控制。

驱动器放大器

MAX2065包括一个22dB固定增益的高性能驱动器。该驱动器放大器优化于50MHz至1000MHz频率范围的高线性度指标。

应用信息

SPI接口和衰减器设置

该数字衰减器可采用5位字节通过3线SPI/MICROWIRE™兼容串行接口进行控制。移入28位数据，MSB在前，并通过 $\overline{CS}$ 打包。当 $\overline{CS}$ 为低电平时，时钟有效，数据在时钟的上升沿移入。当 $\overline{CS}$ 跳变到高电平时，数据被锁存，改变衰减器设置(图1)。表2给出了SPI数据格式的详细信息。

表1. 控制逻辑

VDAC_EN	SER/PAR	VREF_SELECT	ANALOG ATTENUATOR	DIGITAL ATTENUATOR	D/A CONVERTER
0	0	X	Controlled by external control voltage	Parallel controlled	Disabled
1	0	1	Controlled by on-chip DAC	Parallel controlled	Enabled (DAC uses on-chip voltage reference)
0	1	X	Controlled by external control voltage	SPI controlled	Disabled
1	1	0	Controlled by on-chip DAC	SPI controlled	Enabled (DAC uses external voltage reference)

X = 无关。

MICROWIRE是National Semiconductor Corp.的商标。

50MHz至1000MHz高线性度、可串行/
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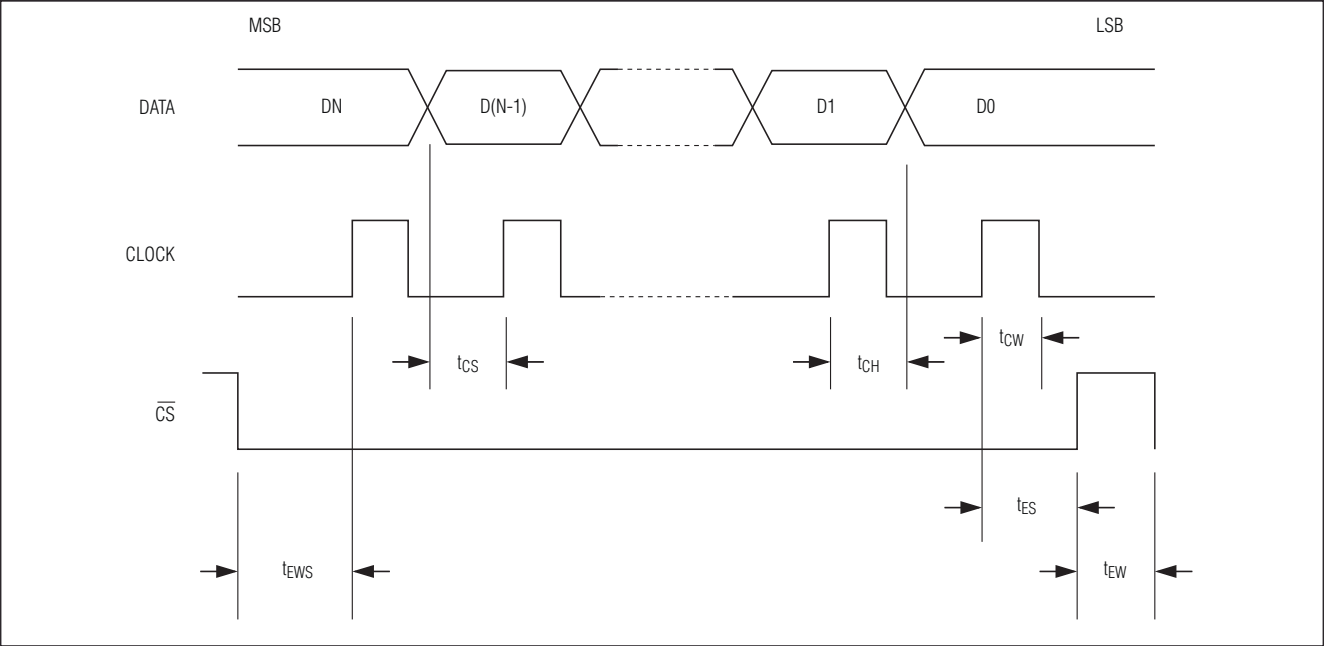


图1. MAX2065 SPI时序图

表2. SPI数据格式

FUNCTION	BIT	DESCRIPTION
Digital Attenuator State 4	D27 (MSB)	16dB step (MSB of the 5-bit word used to program the digital attenuator state 4)
	D26	8dB step
	D25	4dB step
	D24	2dB step
	D23 (LSB)	1dB step (LSB)
Digital Attenuator State 3	D22	5-bit word used to program the digital attenuator state 3 (see the description for digital attenuator state 4)
	D21	
	D20	
	D19	
	D18	
Digital Attenuator State 2	D17	5-bit word used to program the digital attenuator state 2 (see the description for digital attenuator state 4)
	D16	
	D15	
	D14	
	D13	
Digital Attenuator State 1	D12	5-bit word used to program the digital attenuator state 1 (see the description for digital attenuator state 4)
	D11	
	D10	
	D9	
	D8	

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

表2. SPI数据格式(续)

FUNCTION	BIT	DESCRIPTION
On-Chip DAC	D7	Bit 7 (MSB) of on-chip DAC used to program the analog attenuator
	D6	Bit 6 of DAC
	D5	Bit 5 of DAC
	D4	Bit 4 of DAC
	D3	Bit 3 of DAC
	D2	Bit 2 of DAC
	D1	Bit 1 of DAC
	D0 (LSB)	Bit 0 (LSB) of the on-chip DAC

衰减器和DAC操作

在ANALOG_VCTRL (第39引脚)施加一个外部控制电压或通过片上8位DAC控制模拟衰减器,也可以通过SPI兼容接口或并行总线控制数字衰减器。DAC使能/禁止逻辑输入引脚(VDAC_EN)、数字衰减器SPI或并行控制选择逻辑输入(SER/PAR)以及DAC基准电压选择逻辑输入引脚(VREF_SELECT)决定以何种方式控制这些衰减器。可以使能或禁止片上DAC,当DAC使能时,允许选择内部基准或外部基准。请参考表1所示衰减器和DAC工作真值表。

利用并行控制总线设置数字衰减器

为了达到25ns的快速切换能力,MAX2065提供一个辅助的5位并行控制接口。这些数字逻辑衰减器控制引脚(D0–D4)用于设置衰减器的工作状态(表3)。

直接访问5位总线可以使用户省去SPI接口的编程延时。任何SPI总线的速率都受限于指令逐位传递到外围器件的时间。通过直接访问5位并行接口,用户可以在“快速建立”自动增益控制(AGC)应用是实现数字衰减状态的迅速切换。

“速射”预编程衰减状态

MAX2065能够在4个预置衰减等级之间提供“速射”增益选择。与上述辅助5位总线类似,“速射”增益选择能够快速进入4个预先设定的数字衰减状态的任意一个,消除了通过SPI总线进行设置的相关延时。

这种方式的切换速度与采用辅助5位并行总线的速度相当。但这一特殊功能可以使衰减器的数字控制I/O降低5倍或2.5倍(5个控制位相比于1个或2个控制位),具体取决于所要求的状态数。

表3. 数字衰减器设置(并行控制)

INPUT	LOGIC = 0 (OR GROUND)	LOGIC = 1
D0	Disable 1dB attenuator, or when SPI is default programmer	Enable 1dB attenuator
D1	Disable 2dB attenuator, or when SPI is default programmer	Enable 2dB attenuator
D2	Disable 4dB attenuator, or when SPI is default programmer	Enable 4dB attenuator
D3	Disable 8dB attenuator, or when SPI is default programmer	Enable 8dB attenuator
D4	Disable 16dB attenuator, or when SPI is default programmer	Enable 16dB attenuator

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

用户可通过STATE_A和STATE_B输入引脚设置所要求的状态(表4)。利用STATE_A引脚(1个控制位)可以得到2个预先设定的衰减状态,同时使用STATE_A和STATE_B引脚(2个控制位),可以得到4个预先设定的衰减状态。

例如,假设AGC应用需要静态调节衰减器,以调整接收器增益。该AGC电路还需要对可能引起接收器灵敏度下降以及ADC过驱动的干扰信号进行动态衰减。该实例中,MAX2065可以预先设置(通过SPI总线) 2种衰减状态:一个状态用于处理静态增益调节,另一个状态用于处理干扰信号。用户只需要对一个I/O引脚(即STATE_A)进行控制,即可在静态和动态衰减控制之间快速切换。

表4. 预编程衰减状态设置

STATE_A	STATE_B	DIGITAL ATTENUATOR
0	0	Preprogrammed attenuation state 1
1	0	Preprogrammed attenuation state 2
0	1	Preprogrammed attenuation state 3
1	1	Preprogrammed attenuation state 4

表5. 典型应用电路元件值(HC模式)

DESIGNATION	VALUE	SIZE	VENDOR	DESCRIPTION
C1, C2, C7, C11	10nF	0402	Murata Mfg. Co., Ltd.	X7R
C3, C4, C6, C8, C9, C10	1000pF	0402	Murata Mfg. Co., Ltd.	C0G ceramic capacitor
C12, C13	150pF	0402	Murata Mfg. Co., Ltd.	C0G ceramic capacitor
L1	470nH	1008	Coilcraft, Inc.	1008CS-471XJLC
R1, R1A	10 Ω	0402	Panasonic Corp.	1%
R2 (+3.3V applications only)	1k Ω	0402	Panasonic Corp.	1%
R3 (+3.3V applications only)	2k Ω	0402	Panasonic Corp.	1%
R4 (+5V applications and using internal DAC only)	47k Ω	0402	Panasonic Corp.	1%
U1	—	40-pin thin QFN-EP (6mm x 6mm)	Maxim Integrated Products, Inc.	MAX2065ETL+

需要时,用户还可以使用第二个I/O引脚,即STATE_B控制引脚,设置另外2个衰减状态。这两个附加的衰减设置非常适合软件定义的无线通信装置,这些装置往往需要多个静态增益设置,以满足不同工作频率的要求;也需要多个动态衰减设置以处理不同阻塞电平(由多个无线通信标准定义)。

串联OIP3

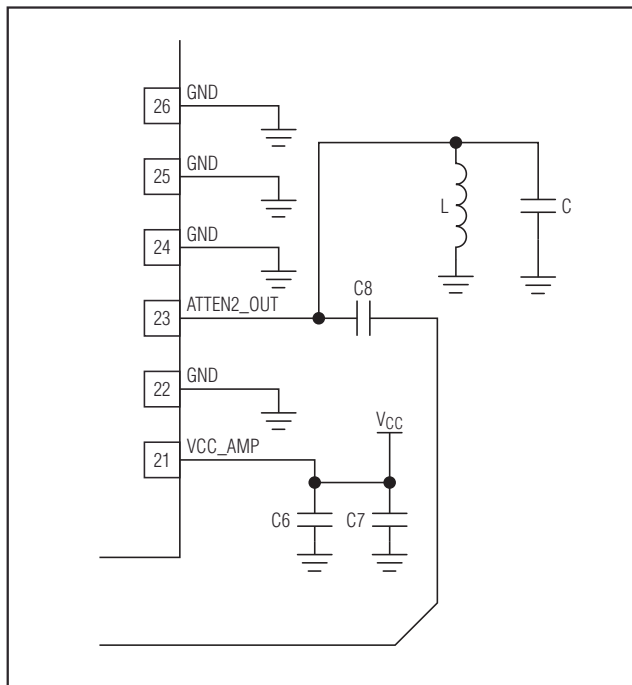
考虑到两个衰减器的有限IP3指标,当两个衰减器都设置在较高的衰减等级时,将会劣化串联OIP3。

外部偏置

驱动放大器偏置电流可通过外部电阻设置并进行优化。将电阻R1和R1A连接到RSET (引脚18),可以设置放大器的偏置电流。增大外部偏置电阻可降低工作电流,代价是降低系统性能。

MAX2065

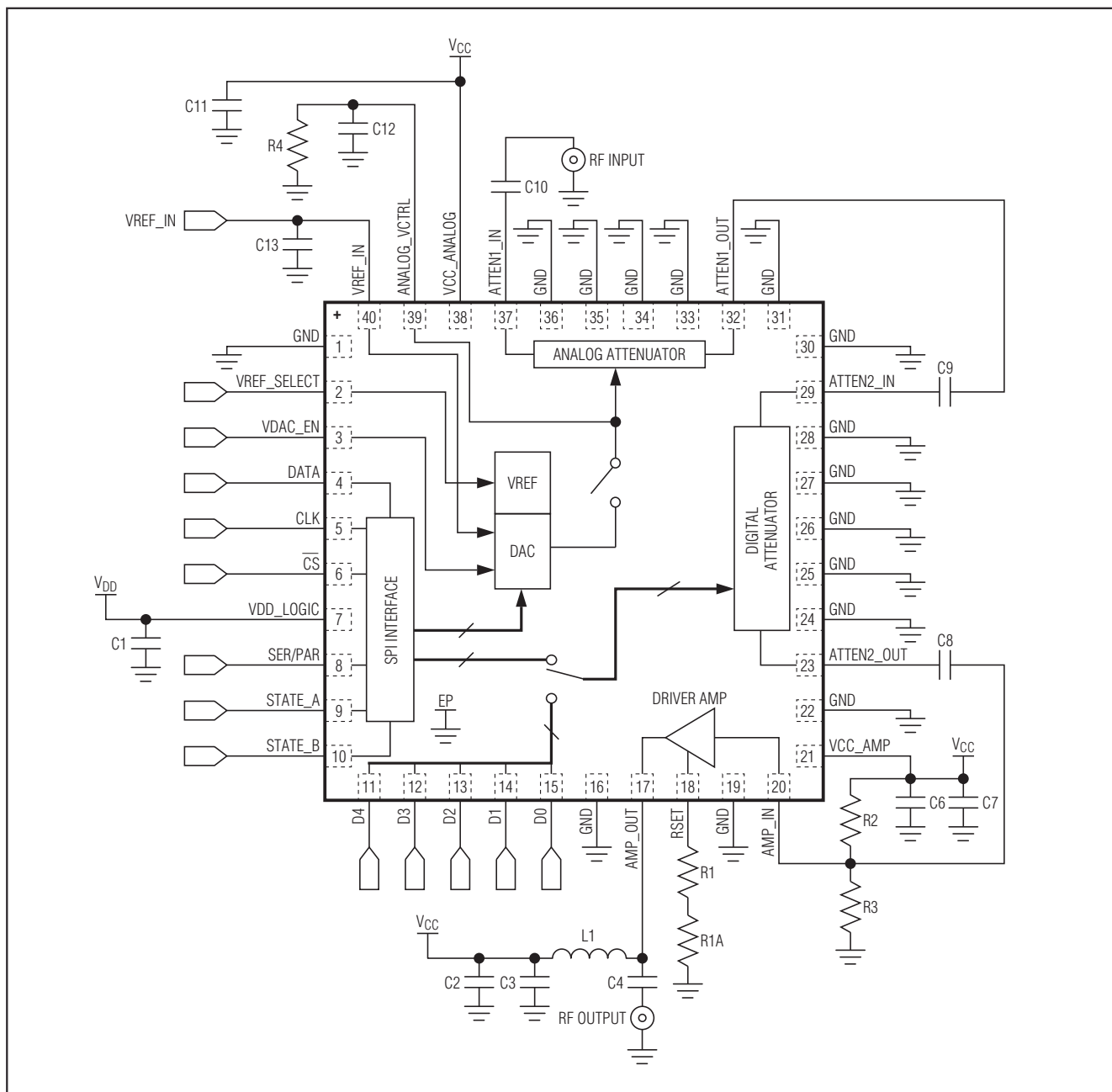
DESIGNATION	VALUE	SIZE	VENDOR	DESCRIPTION
C1, C2, C7, C11	10nF	0402	Murata Mfg. Co., Ltd.	X7R
C3, C4, C6, C8, C9, C10	1000pF	0402	Murata Mfg. Co., Ltd.	C0G ceramic capacitor
C12, C13	150pF	0402	Murata Mfg. Co., Ltd.	C0G ceramic capacitor
L1	470nH	1008	Coilcraft, Inc.	1008CS-471XJLC
R1	24Ω	0402	Vishay	1%
R1A	0.01μF	0402	Murata Mfg. Co., Ltd.	X7R
R2 (+3.3V applications only)	1kΩ	0402	Panasonic Corp.	1%
R3 (+3.3V applications only)	2kΩ	0402	Panasonic Corp.	1%
R4 (+5V applications and using internal DAC only)	47kΩ	0402	Panasonic Corp.	1%
U1	—	40-pin thin QFN-EP (6mm x 6mm)	Maxim Integrated Products, Inc.	MAX2065ETL+



23

50MHz至1000MHz高线性度、可串行/并行控制的模拟/数字VGA

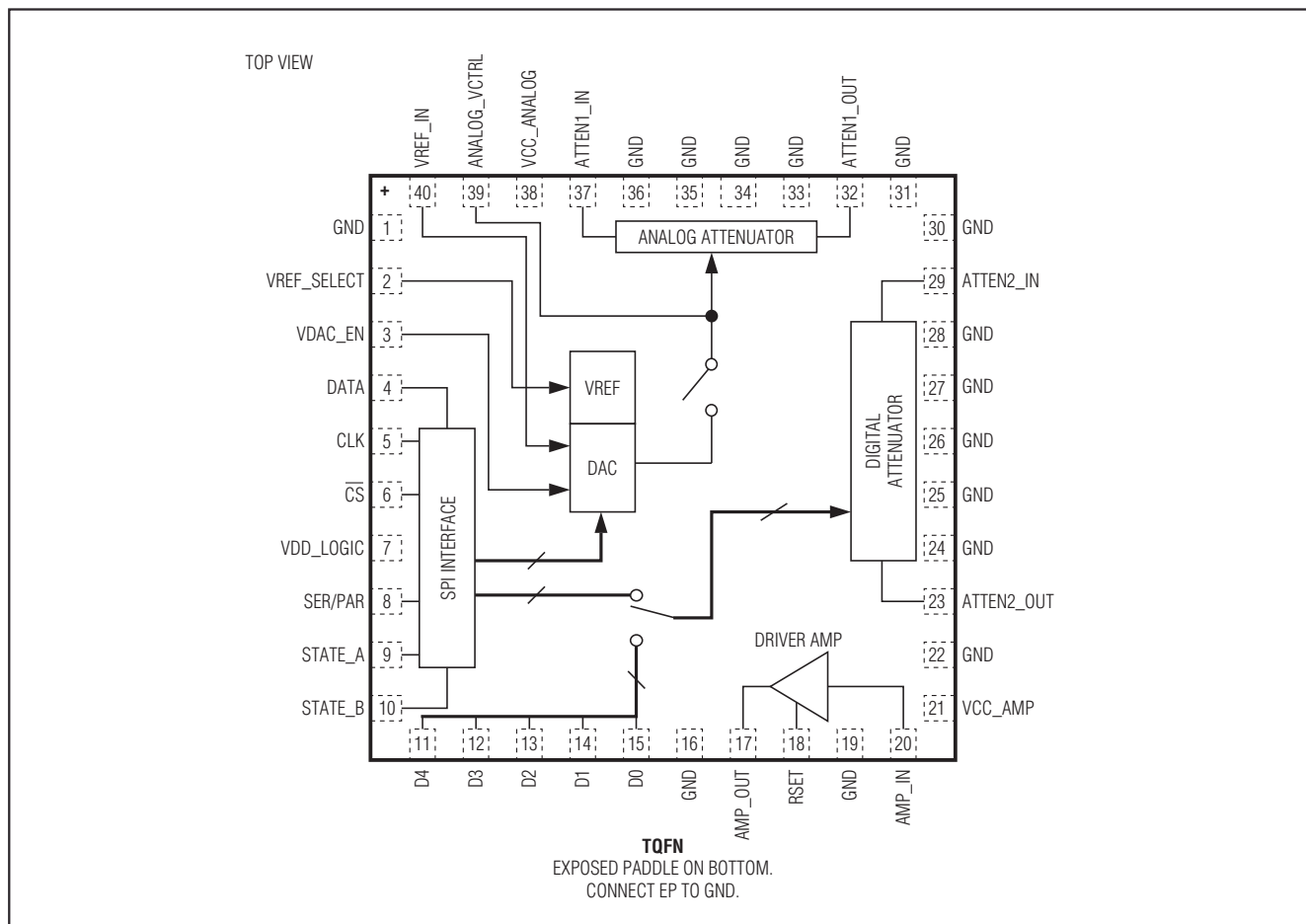
典型应用电路



50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

引脚配置/功能框图

MAX2065



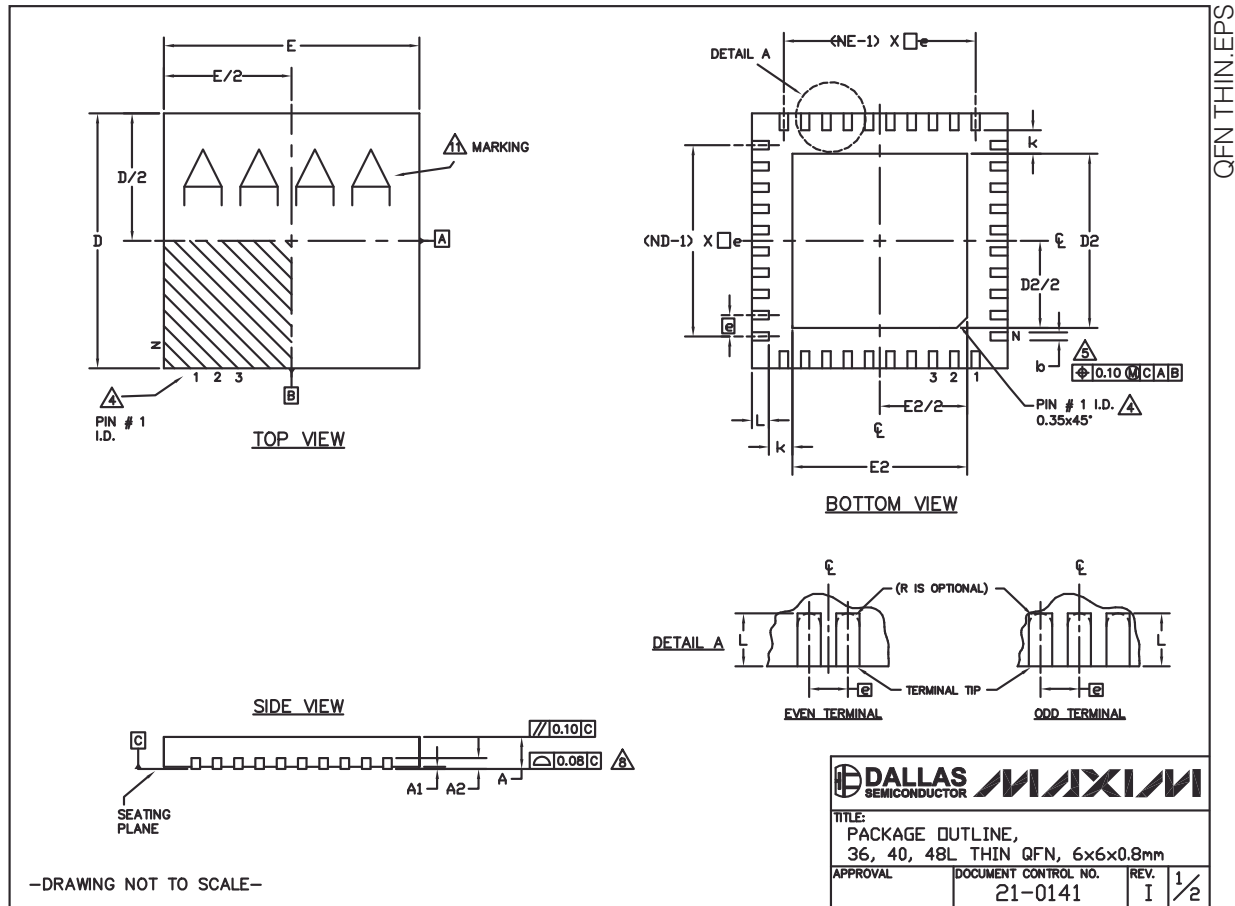
芯片信息

PROCESS: SiGe BiCMOS

50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

封装信息

(本数据资料提供的封装图可能不是最近的规格，如需最近的封装外形信息，请查询 www.maxim-ic.com.cn/packages。)



50MHz至1000MHz高线性度、可串行/ 并行控制的模拟/数字VGA

封装信息(续)

(本数据资料提供的封装图可能不是最近的规格，如需最近的封装外形信息，请查询 www.maxim-ic.com.cn/packages.)

MAX2065

COMMON DIMENSIONS									
PKG.	36L 6x6			40L 6x6			48L 6x6		
SYMBOL	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80
A1	0	0.02	0.05	0	0.02	0.05	0	—	0.05
A2	0.20 REF.			0.20 REF.			0.20 REF.		
b	0.20	0.25	0.30	0.20	0.25	0.30	0.15	0.20	0.25
D	5.90	6.00	6.10	5.90	6.00	6.10	5.90	6.00	6.10
E	5.90	6.00	6.10	5.90	6.00	6.10	5.90	6.00	6.10
e	0.50 BSC.			0.50 BSC.			0.40 BSC.		
k	0.25	—	—	0.25	—	—	0.25	—	—
L	0.35	0.50	0.65	0.30	0.40	0.50	0.30	0.40	0.50
N	36			40			48		
ND	9			10			12		
NE	9			10			12		
JEDEC	WJJD-1			WJJD-2			—		

EXPOSED PAD VARIATIONS						
PKG. CODES	D2			E2		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
T3666-2	3.60	3.70	3.80	3.60	3.70	3.80
T3666-3	3.60	3.70	3.80	3.60	3.70	3.80
T3666N-1	3.60	3.70	3.80	3.60	3.70	3.80
T3666MN-1	3.60	3.70	3.80	3.60	3.70	3.80
T4066-2	4.00	4.10	4.20	4.00	4.10	4.20
T4066-3	4.00	4.10	4.20	4.00	4.10	4.20
T4066-5	4.00	4.10	4.20	4.00	4.10	4.20
T4866-1	4.40	4.50	4.60	4.40	4.50	4.60
T4866N-1	4.40	4.50	4.60	4.40	4.50	4.60
T4866-2	4.40	4.50	4.60	4.40	4.50	4.60

NOTES:

1. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
3. N IS THE TOTAL NUMBER OF TERMINALS.
4. THE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION SHALL CONFORM TO JESD 95-1 SPP-012. DETAILS OF TERMINAL #1 IDENTIFIER ARE OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED. THE TERMINAL #1 IDENTIFIER MAY BE EITHER A MOLD OR MARKED FEATURE.
5. DIMENSION b APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.25mm AND 0.30mm FROM TERMINAL TIP.
6. ND AND NE REFER TO THE NUMBER OF TERMINALS ON EACH D AND E SIDE RESPECTIVELY.
7. DEPOPULATION IS POSSIBLE IN A SYMMETRICAL FASHION.
8. COPLANARITY APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.
9. DRAWING CONFORMS TO JEDEC MO220, EXCEPT FOR 0.4mm LEAD PITCH PACKAGE T4866-1.
10. WARPAGE SHALL NOT EXCEED 0.10mm.
11. MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.
12. NUMBER OF LEADS SHOWN FOR REFERENCE ONLY.
13. ALL DIMENSIONS APPLY TO BOTH LEADED (-) AND PbFREE (+) PKG. CODES.

—DRAWING NOT TO SCALE—

 DALLAS SEMICONDUCTOR 	
TITLE: PACKAGE OUTLINE, 36, 40, 48L THIN QFN, 6x6x0.8mm	
APPROVAL	DOCUMENT CONTROL NO. 21-0141
	REV. I

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